

Some Extra Reading on Topological Quantum Computation

Review Articles:

- Nayak, Chetan; Simon, Steven H.; Stern, Ady; et al., Non-Abelian anyons and topological quantum computation, *REVIEWS OF MODERN PHYSICS* **80**, 1083-1159 (2008)
- Alicea, Jason, New directions in the pursuit of Majorana fermions in solid state systems, *REPORTS ON PROGRESS IN PHYSICS* **75**, 076501 (2012)
- Ananda Roy, David P. DiVincenzo, Topological Quantum Computing, arXiv:1701.05052 (2017)

Original Research:

- Sau, Jay D.; Lutchyn, Roman M.; Tewari, Sumanta; et al., Generic New Platform for Topological Quantum Computation Using Semiconductor Heterostructures, *PHYSICAL REVIEW LETTERS* **104**, 040502 (2010)
- Jason Alicea et al., Non-Abelian statistics and topological quantum information processing in 1D wire networks, *Nature Physics* **7**, 412–417 (2011)
- Mourik, V.; Zuo, K.; Frolov, S. M.; et al., Signatures of Majorana Fermions in Hybrid Superconductor-Semiconductor Nanowire Devices, *SCIENCE* **336** 6084, 1003 (2012)

Lecture 9, April 26, 2018

This week:

- Semiconductor quantum dots for QIP
 - Introduction to QDs
 - Single spins for qubits
 - Initialization
 - Read-Out
 - Single qubit gates

Please take a seat
in the front center part of the lecture hall
if you do not mind.

Book on basics:

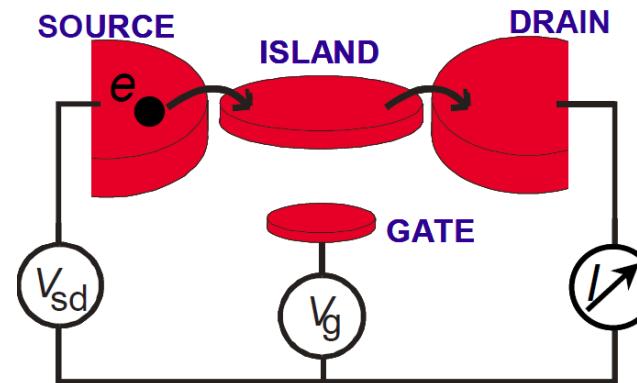
- Thomas Ihn, *Semiconductor Nanostructures: Quantum States and Electronic Transport*, ISBN 978-0-19-953442-5, Oxford University Press, Oxford, 2010.

Introductory Review Articles:

- R. Hanson, L. P. Kouwenhoven, J. R. Petta et al., Spins in few-electron quantum dots, *Reviews of Modern Physics* **79**, 1217 (2007)
- R. Hanson, & D. D. Awschalom, Coherent manipulation of single spins in semiconductors, *Nature* **453**, 1043 (2008)

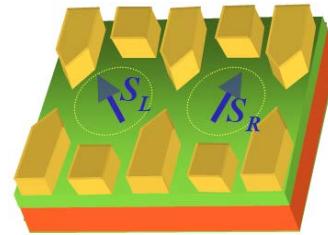
Electrically Controlled and Measured Quantum Dots

A small semiconducting (or metallic) island where electrons are confined, giving a discrete level spectrum



- Coupled via tunnel barriers to source and drain reservoirs
- Coupled capacitively to gate electrode, to control # of electrons

Spin Qubits in Quantum Dots



Loss & DiVincenzo,
PRA 57, 120 (1998)
Vandersypen *et al.*,
Proc. MQC02 (quant-ph/0207059)

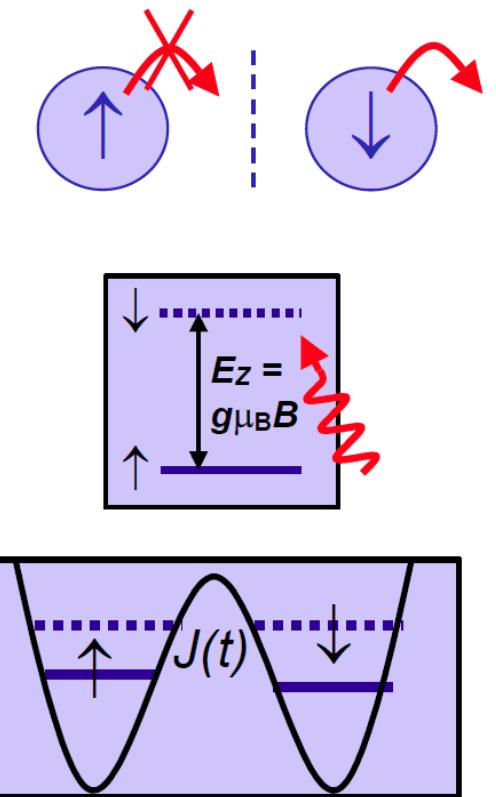
Initialization 1-electron, low T , high B_0
 $H_0 \sim \sum \omega_i \sigma_{zi}$

Read-out convert spin to charge
then measure charge

ESR pulsed microwave magnetic field
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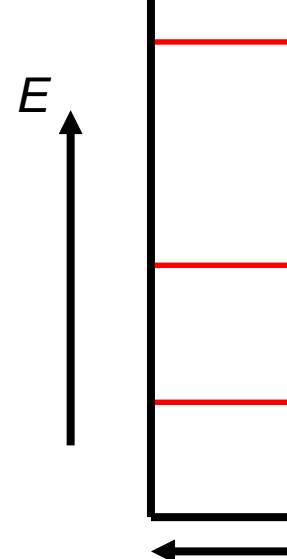
SWAP exchange interaction
 $H_J \sim \sum J_{ij}(t) \sigma_i \cdot \sigma_j$

Coherence long relaxation time T_1
long coherence time T_2



Electrons in Atoms, Quantum Dots

Schrödinger:
electrons in confined systems occupy quantized energy levels



Particle in a box:

$$E_n = \frac{\hbar^2}{2m} \left(\frac{\pi n}{L} \right)^2, \quad n = 1, 2, 3 \dots$$

Pauli:
each level can be occupied with one spin-up
electron and one spin-down electron

QDs: 0.1 meV
Atoms: 10 eV

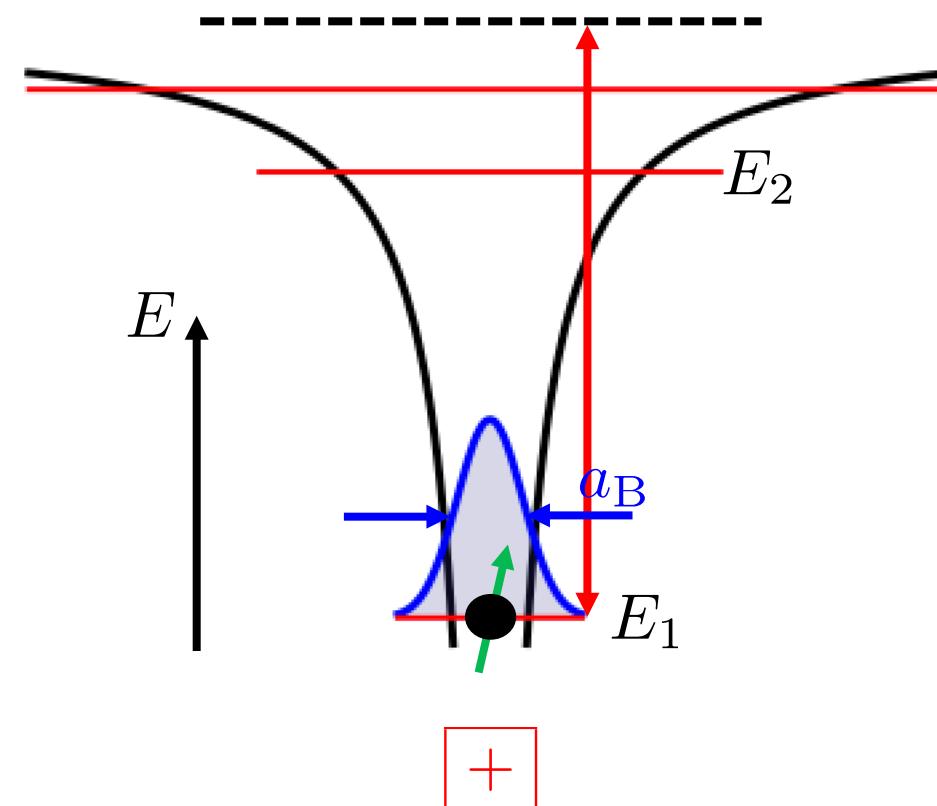
1 meV \sim 250 GHz

The Hydrogen Atom

Quantized energy levels in the hydrogen atom

$$E_n = -\frac{E_{\text{Ry}}}{n^2}, \quad n = 1, 2, 3 \dots$$

Single-particle level spectrum



E. Schrödinger, Phys. Rev. 28, 1049 (1926).

$$E_{\text{Ry}} = \frac{2m}{\hbar^2} \left(\frac{e^2}{8\pi\epsilon_0} \right)^2$$

Atoms: 13.6 eV
GaAs: 6 meV

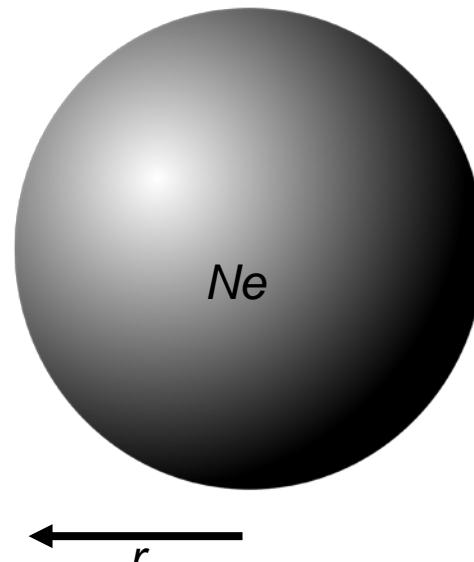
$$a_B = \frac{\hbar^2}{2m} \left(\frac{8\pi\epsilon_0}{e^2} \right)$$

Atoms: 0.53 Å
GaAs: 10 nm

Pauli:
each level can be occupied with one spin-up electron and one spin-down electron

Electrons in Atoms, Quantum Dots

electrons in confined systems interact via Coulomb repulsion



Electrostatic/charging energy

$$E_C = \frac{Q^2}{2C} = \frac{e^2 N^2}{2C}, \quad N \text{ (large) integer}$$

$$C = 4\pi\epsilon\epsilon_0 r \quad (\text{Sphere})$$

$$\Rightarrow E_C = \frac{e^2 N^2}{8\pi\epsilon\epsilon_0 r}, \quad N \text{ (large) integer}$$

QDs: 1 meV
Atoms: 10 eV

Atoms vs. Quantum Dots

	Atom	Quantum dot
Confinement	r^1 , strong, rigid, hard to tune	r^2 , soft, parabolic, tunable
Symmetry	perfect, given by nature	never perfect, hard to achieve
Electrical addressing	hard to achieve	well suitable tunable coupling
Optical addressing	well suitable	well suitable
Coupling to	thermal photons, ...	photons, phonons, other electrons

Both systems give access to single electron/spin manipulation

Lecture 10, May 3, 2018

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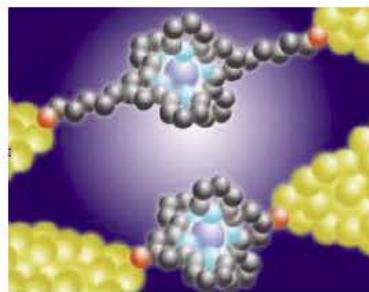
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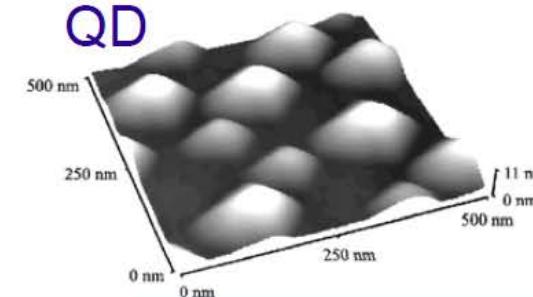
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Examples of Quantum Dots

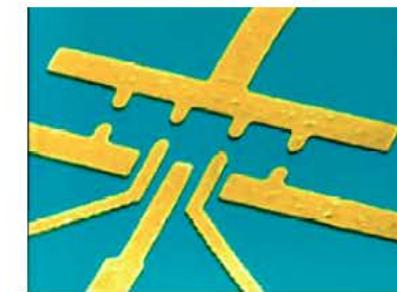
single molecule



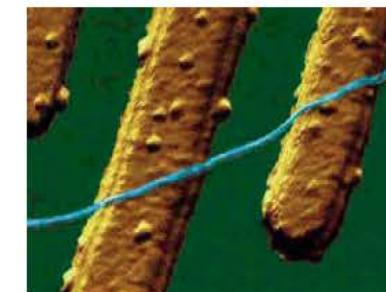
self-assembled QD



lateral QD



nanotube



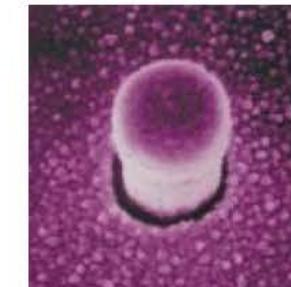
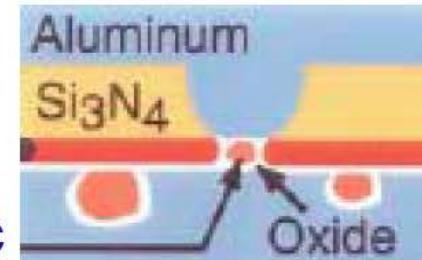
1 nm

10 nm

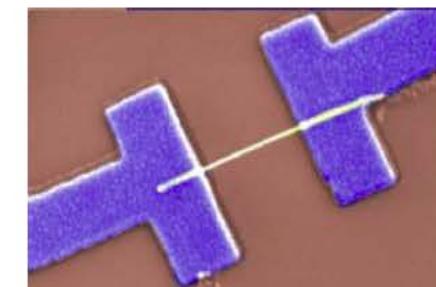
100 nm

1 μm

metallic nanoparticle

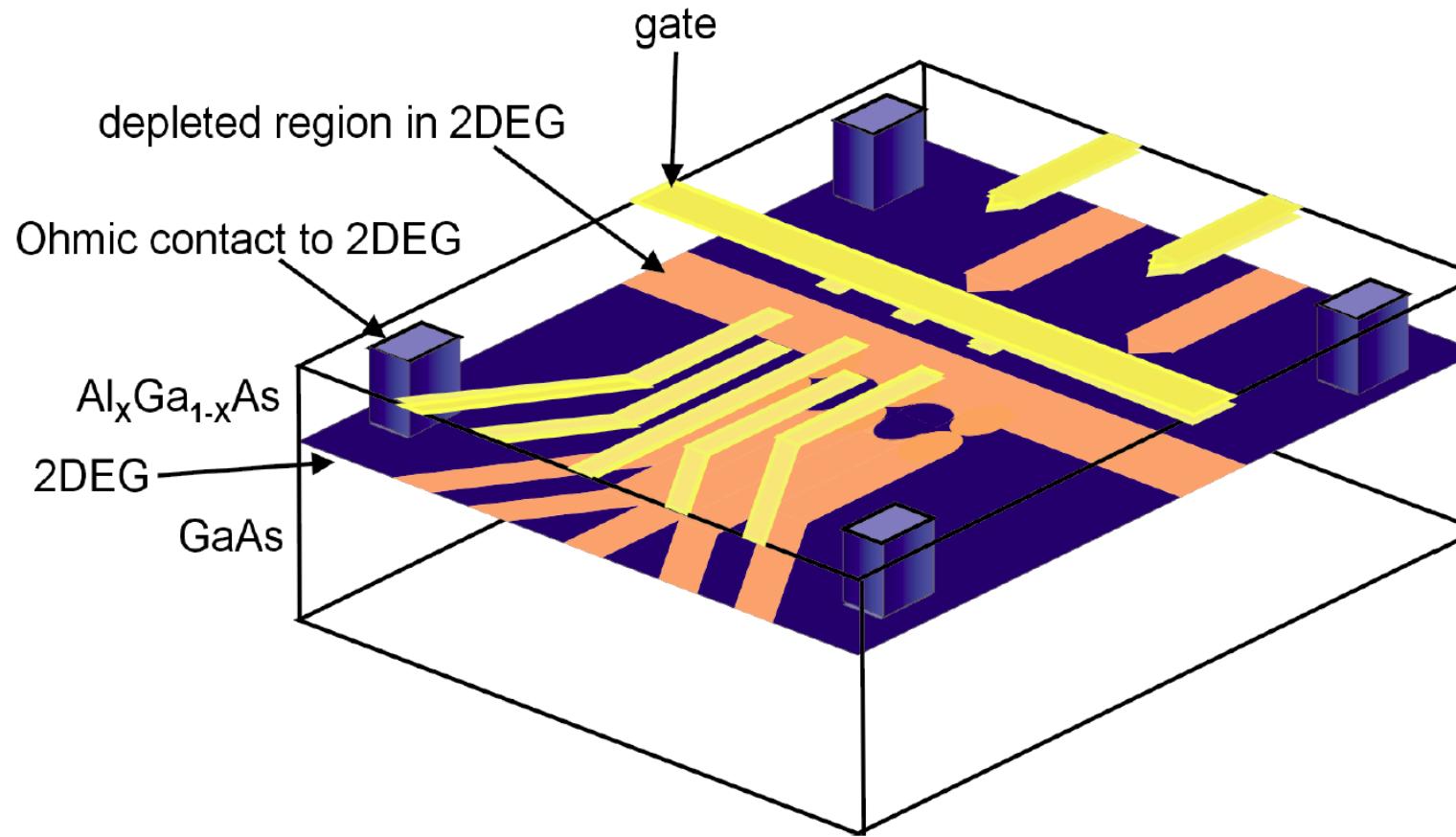


vertical QD

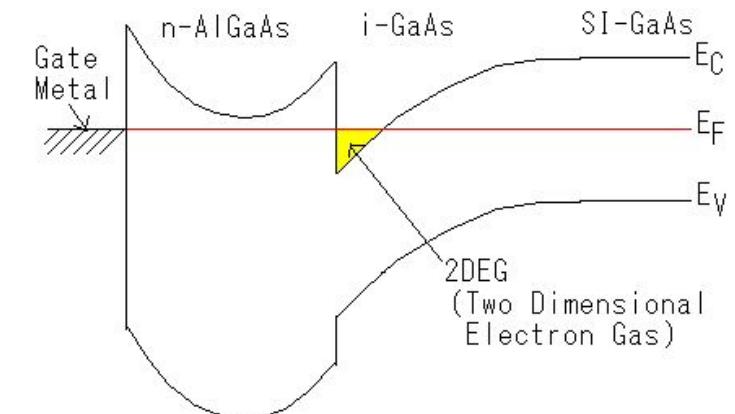


nanowire

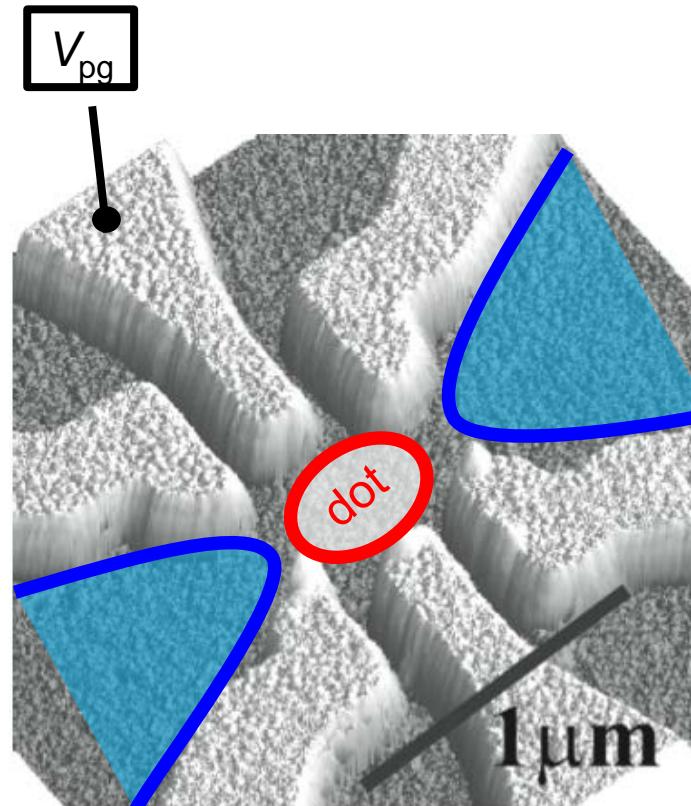
Electrostatically Defined Quantum Dots



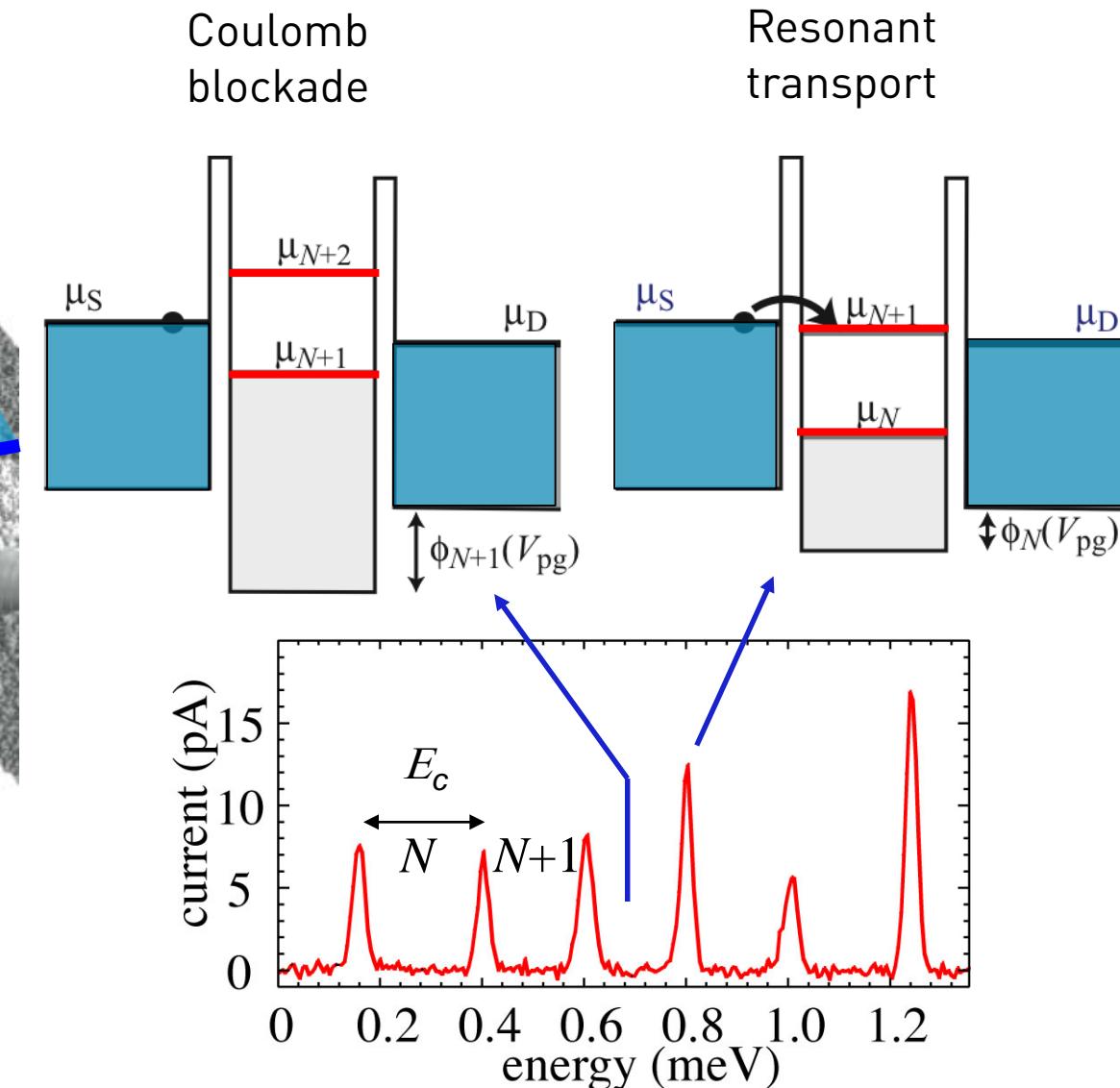
- Electrically measured (contact to 2DEG)
- Electrically controlled number of electrons
- Electrically controlled tunnel barriers



Coulomb Blockade

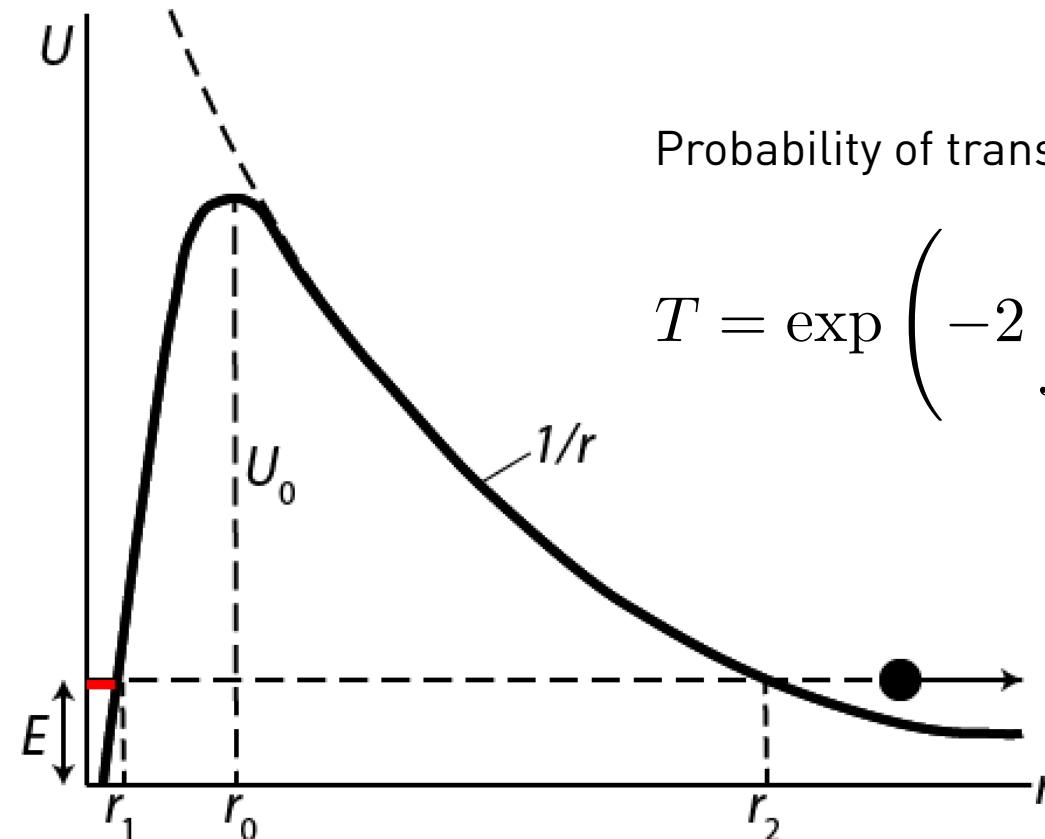


Quantum effects become visible at temperatures $< 4.2\text{ K}$



Tunneling from Discrete Levels

α -decay described by tunneling from quantized levels:



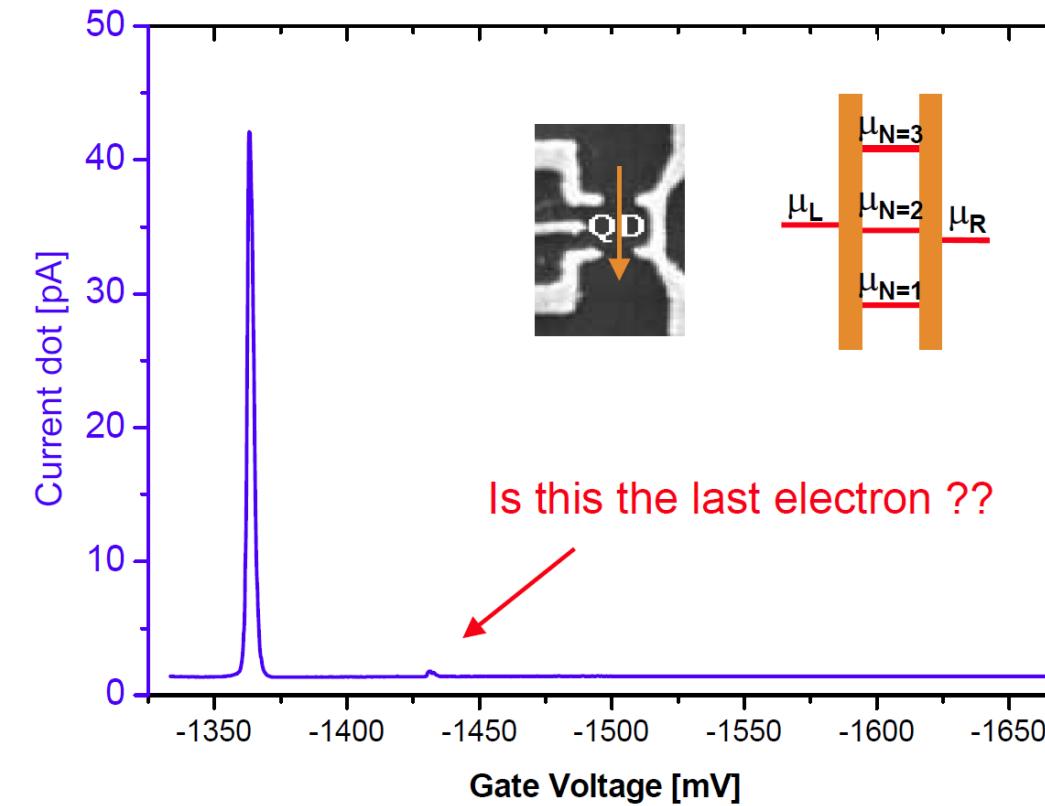
Probability of transmission through barrier (WKB approx.):

$$T = \exp \left(-2 \int_{x_1}^{x_2} \sqrt{\frac{2m[U(x) - E]}{\hbar^2}} dx \right)$$

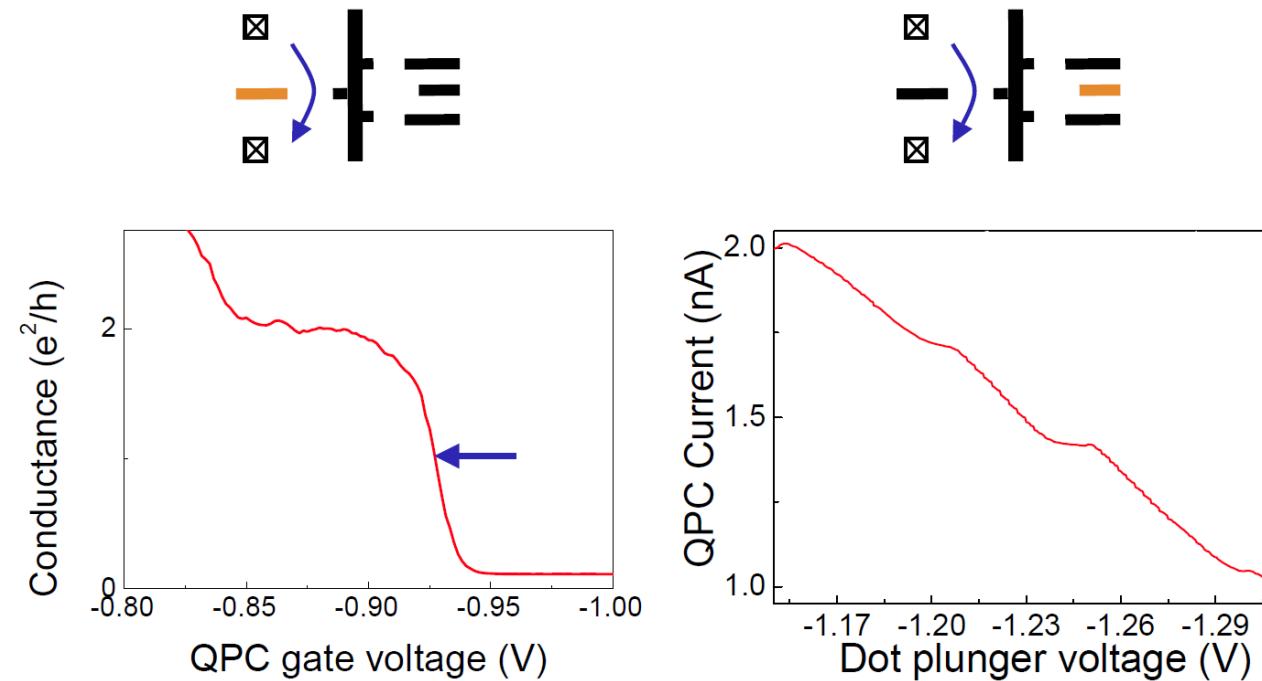
G. Gamov, Z. Phys. 51, 204 (1928).

Slides and material courtesy of Thomas Ihn, ETH Zurich

Transport Through Quantum Dot - Coulomb Blockade



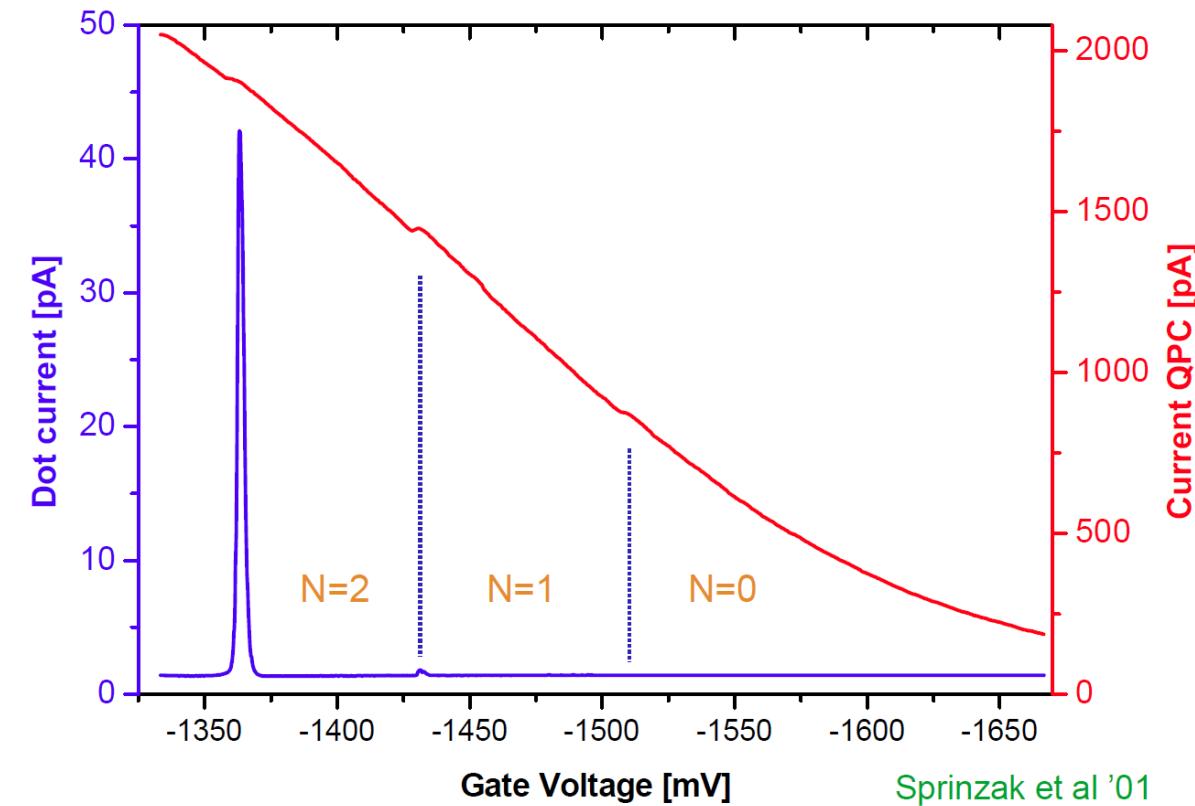
A Quantum Point Contact (QPC) as a Charge Detector



Field *et al*, Phys. Rev. Lett. 70, 1311 (1993)

Slides and material courtesy of Lieven Vandersypen, TU Delft

The Last Electron

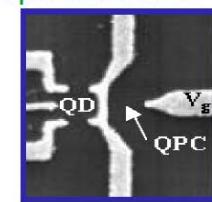


Few-Electron Double Dot Design

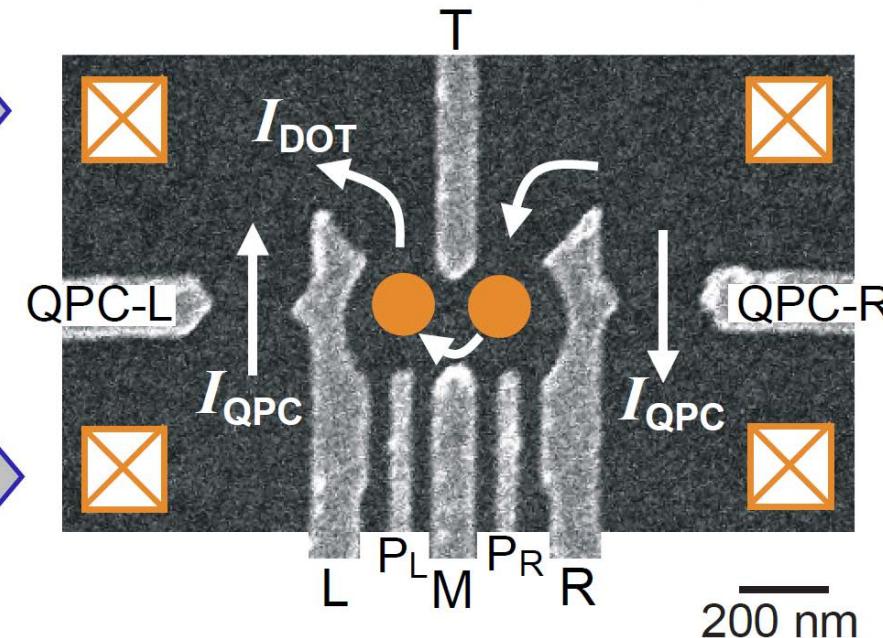
Ciorga et al '99



Open design

Field et al'93
Sprinzak et al '01QPC for charge
detection

Elzerman et al., PRB 2003



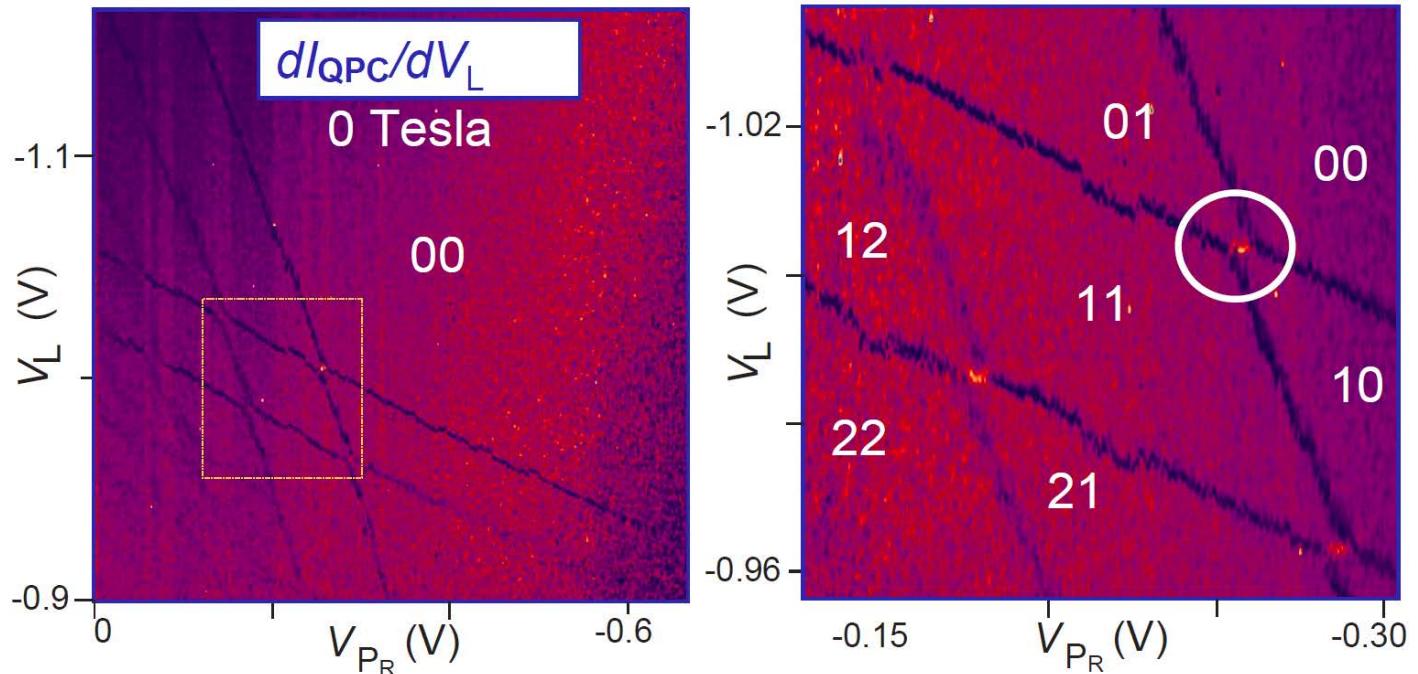
GaAs/AlGaAs wafers:

{ NTT (T. Saku, Y. Hirayama)
 Sumitomo Electric
 Universität Regensburg (W. Wegscheider)

Elzerman et al., *Phys. Rev. B* **67**, 161308(R) (2003)Ciorga et al., *Phys. Rev. B* **61**, R16315(R) (2000)Field et al, *Phys. Rev. Lett.* **70**, 1311 (1993)Sprinzak et al *Phys. Rev. Lett.* **88**, 176805 (2002)

Slides and material courtesy of Lieven Vandersypen, TU Delft

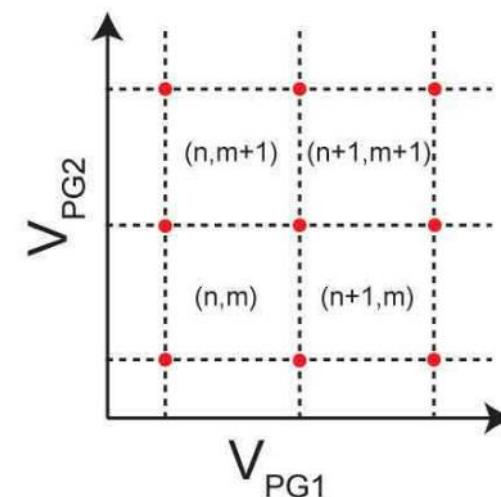
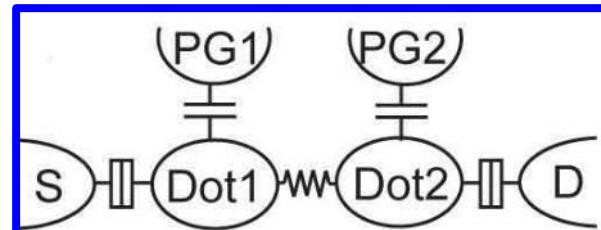
Few-Electron Double Dot Measured via QPC



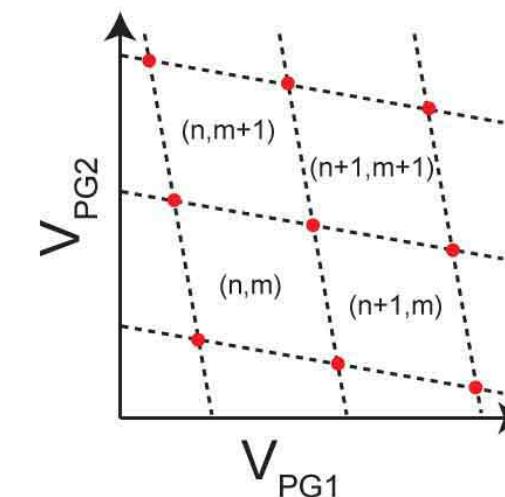
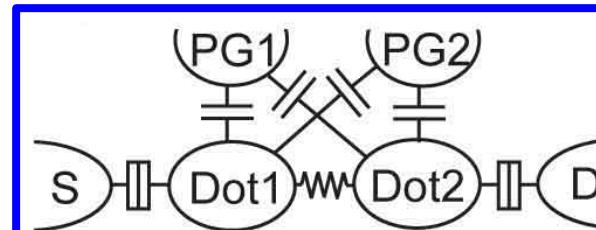
- Double dot can be emptied
- QPC can detect all charge transitions

Double Dot Charge Stability Diagram

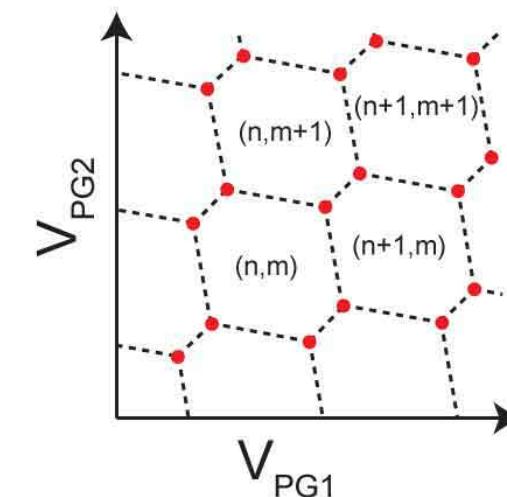
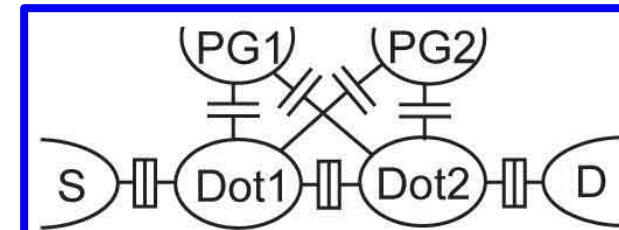
$$\text{---} = \begin{array}{c} \text{---} \\ \text{---} \\ \text{---} \end{array}$$



each dot coupled
only to its gate



each dot coupled
to both gates



both dots coupled to
each other

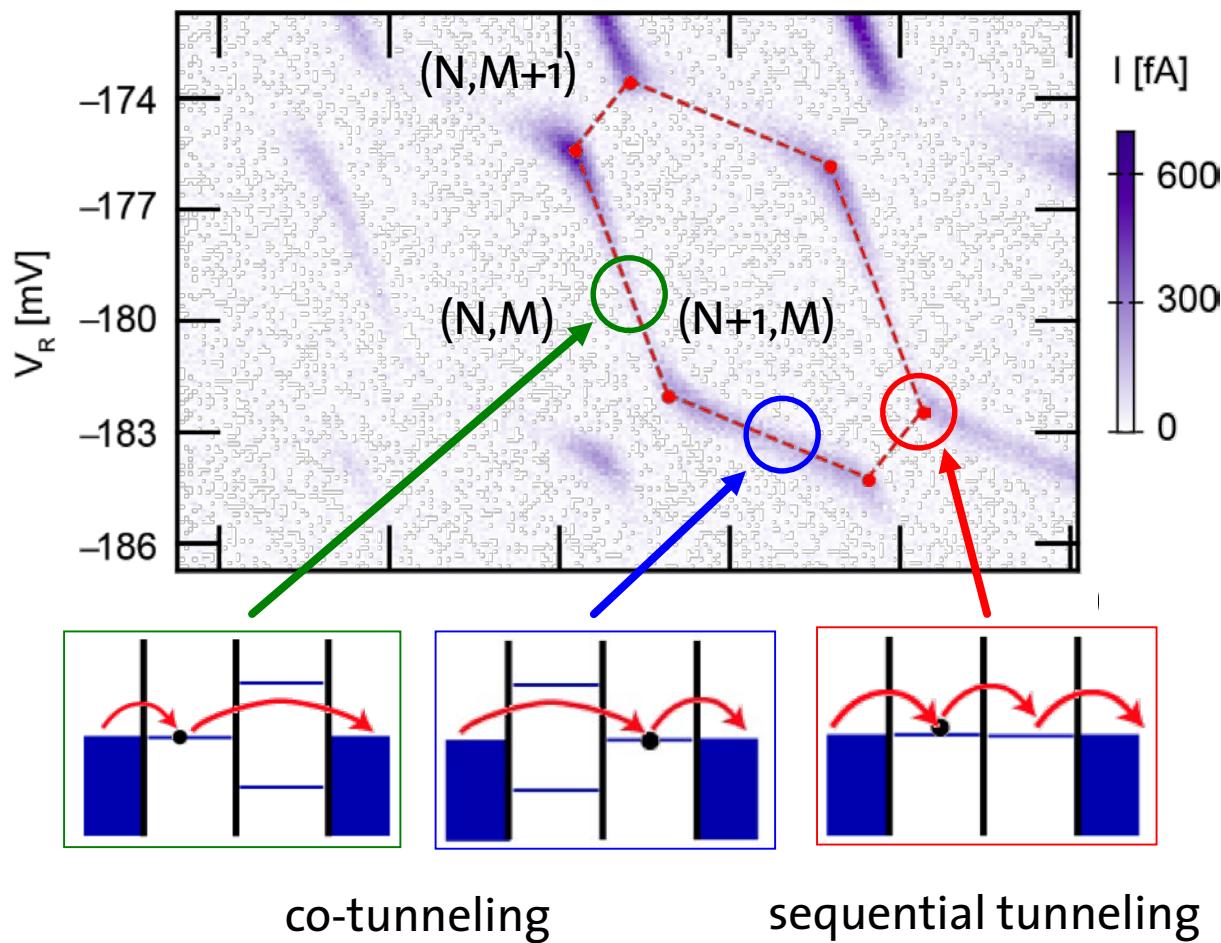
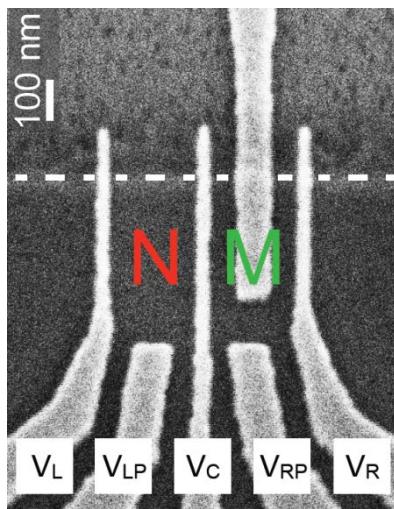
Double Dot Current

Transport measurements:

- Charging diagrams

dot properties:

- many electron regime
- large charging energy
- consider two-level approx.



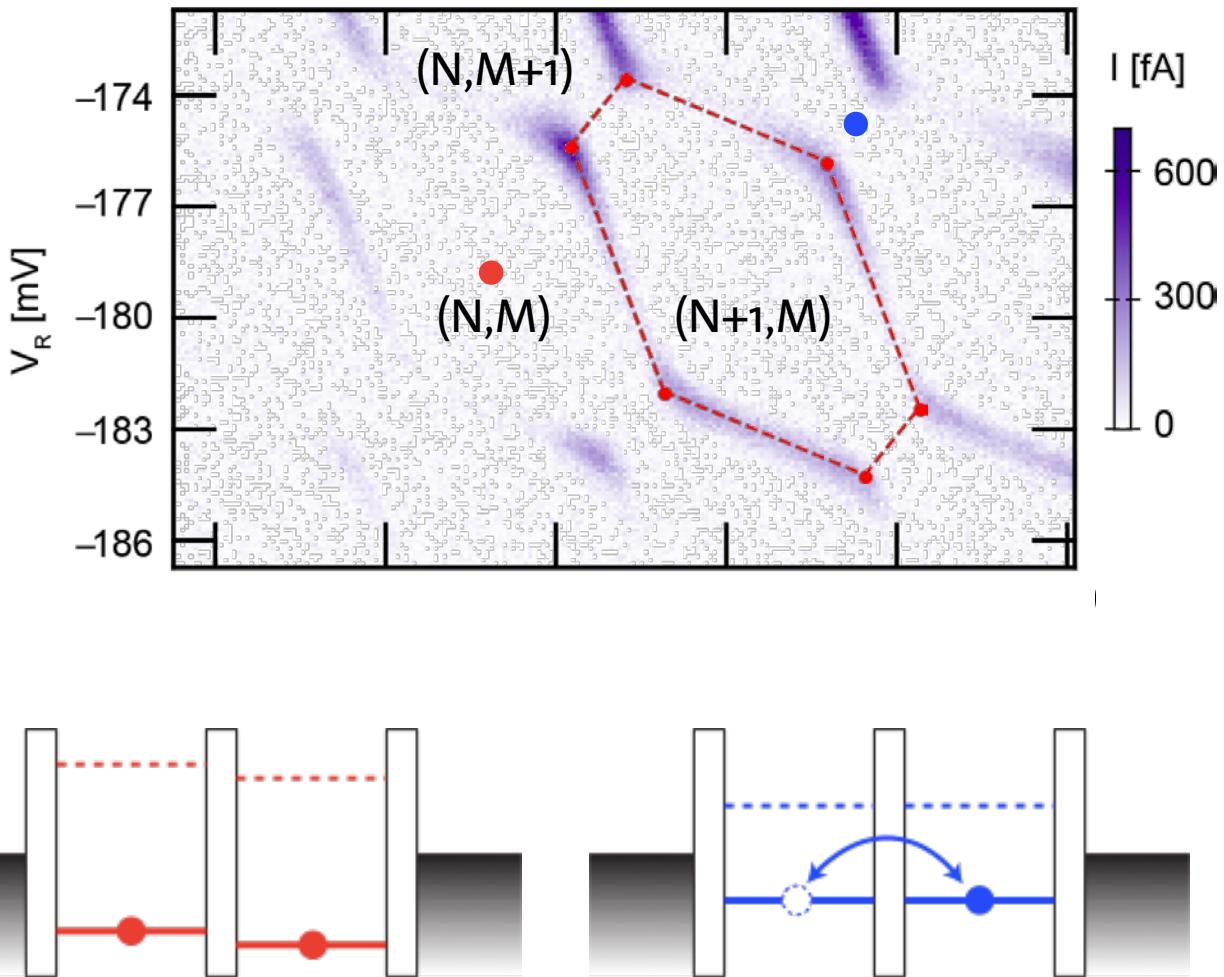
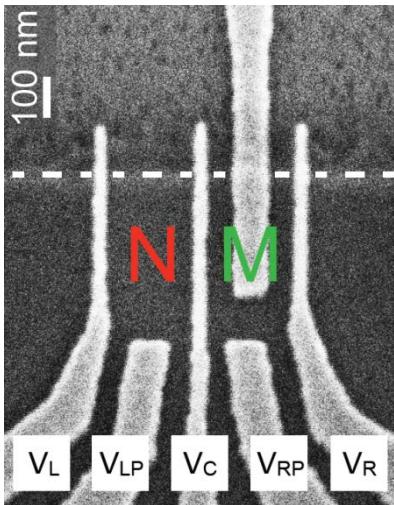
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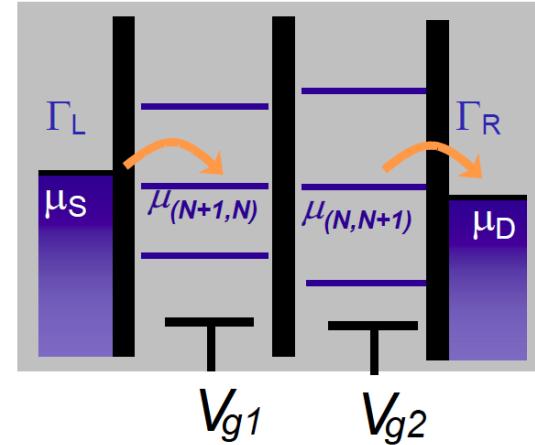
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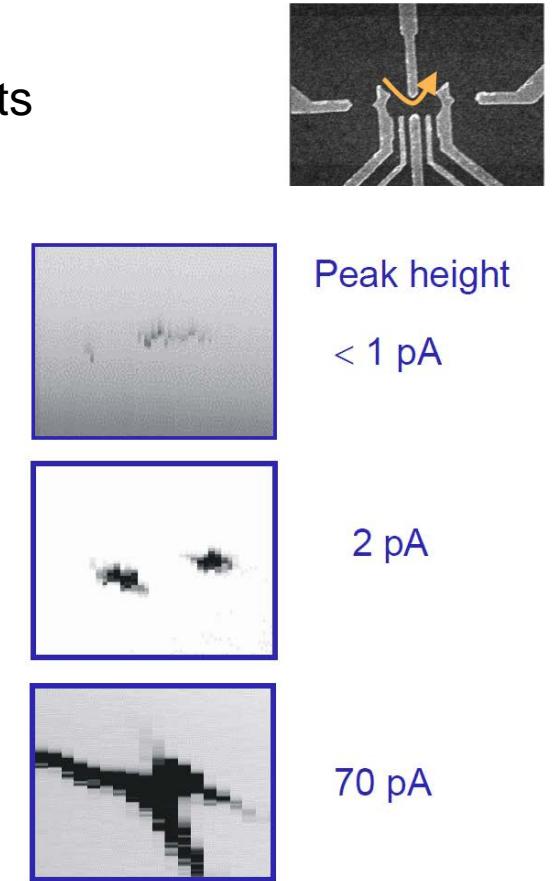
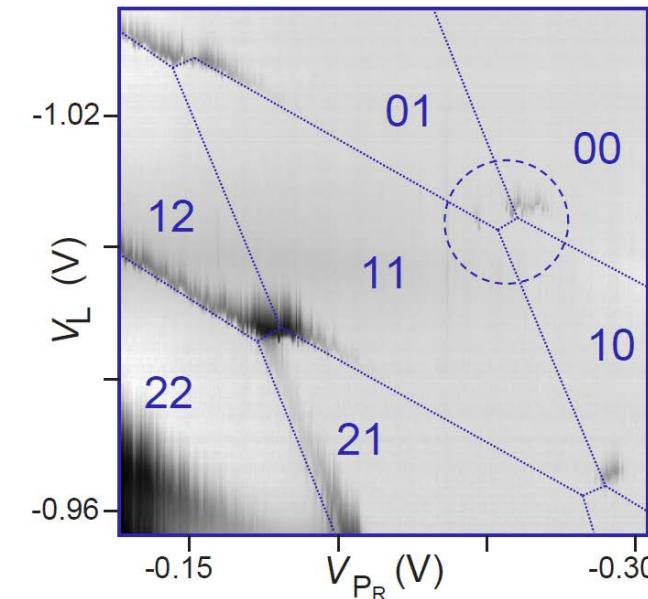
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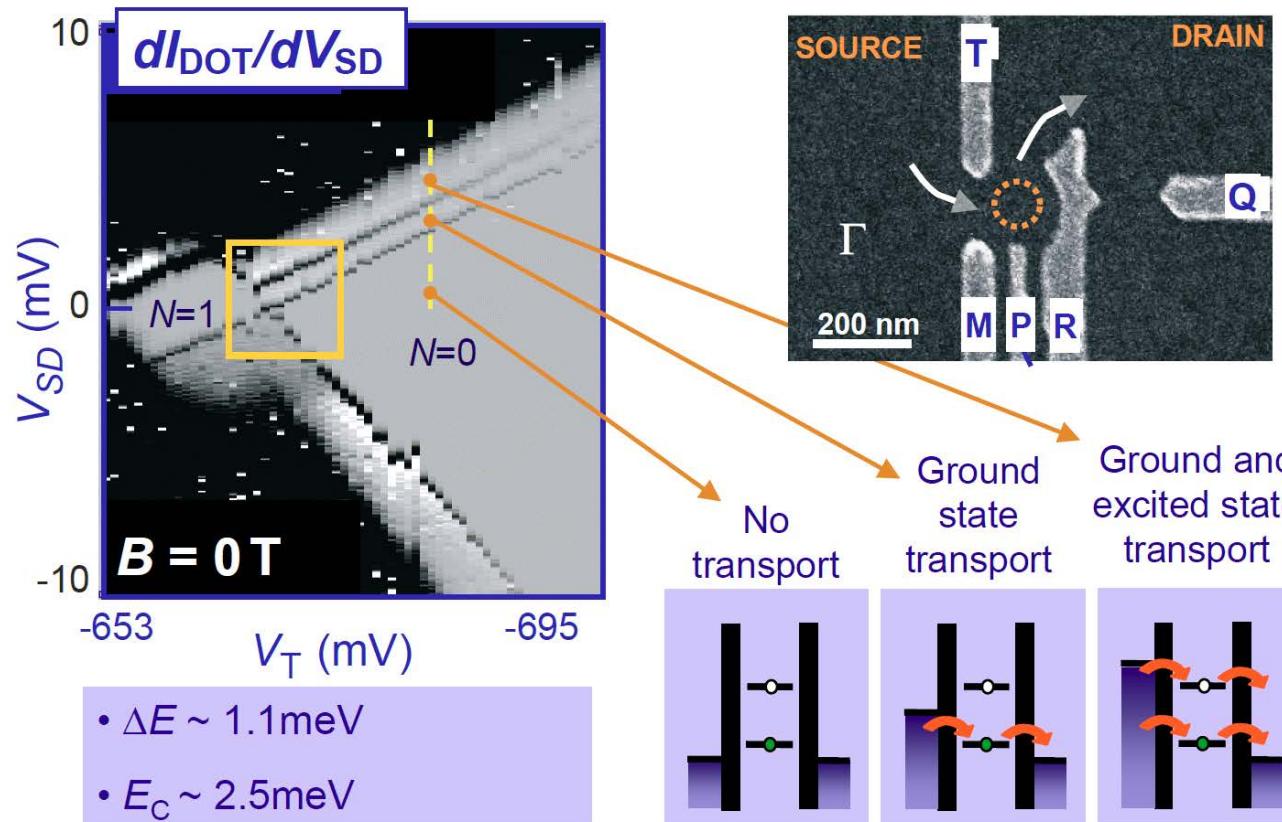
Single Electron Tunneling Through Two Dots in Series



Few-electron double dot:
Transport current through dots

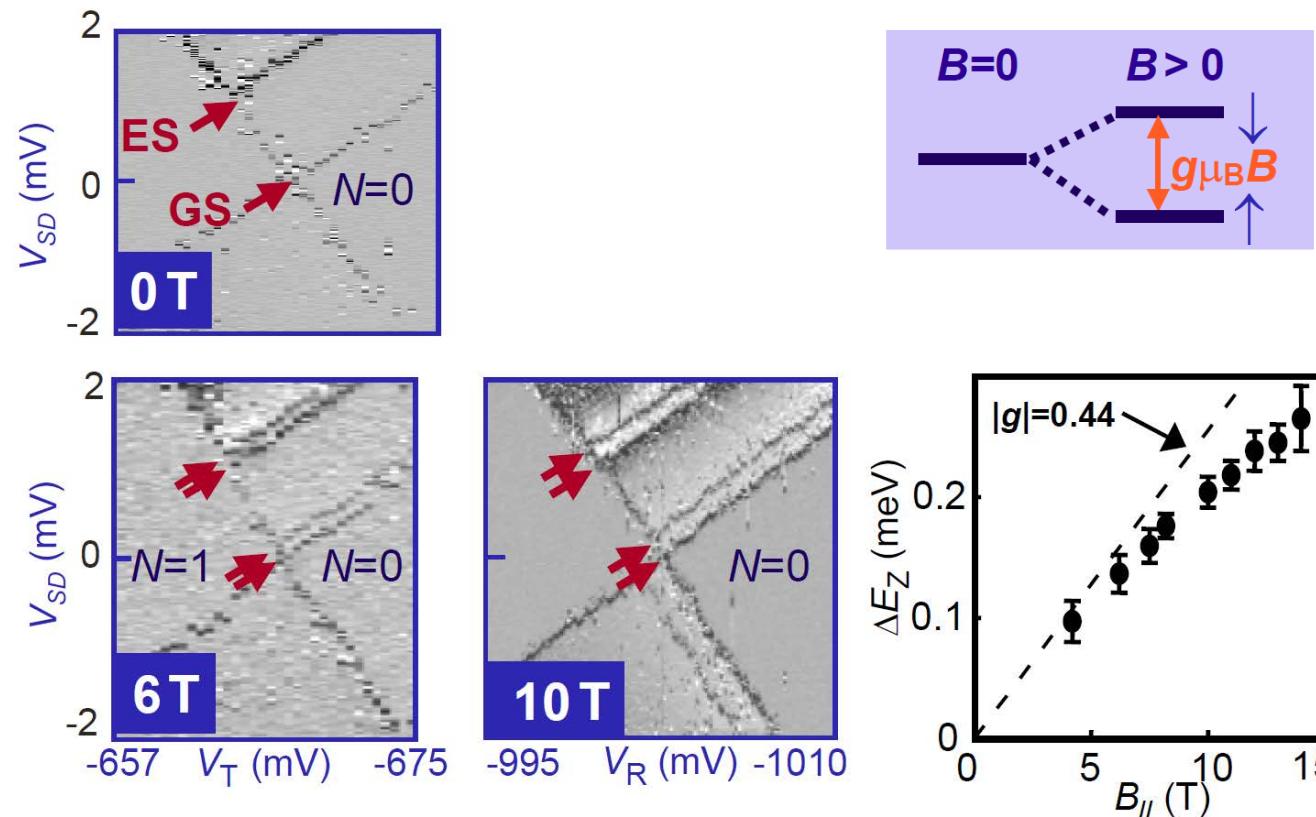


Energy Level Spectroscopy at $B = 0$



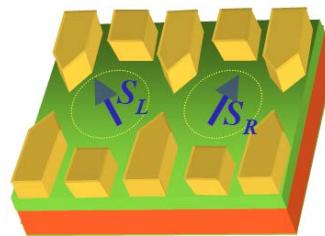
J. Elzerman *et al.*, Phys. Rev. B 67, 161308(R) (2003)
 Slides and material courtesy of Lieven Vandersypen, TU Delft

Single Electron Zeeman Splitting in B_{\parallel}



Hanson et al, *Phys. Rev. Lett.* **91**, 196802 (2003)
 Also: Potok et al, *Phys. Rev. Lett.* **91**, 016802 (2003)
 Slides and material courtesy of Lieven Vandersypen, TU Delft

Spin Qubits in Quantum Dots



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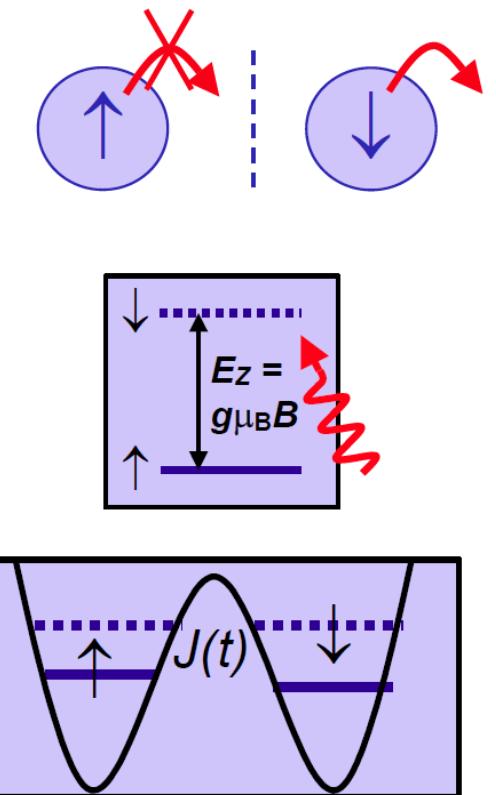
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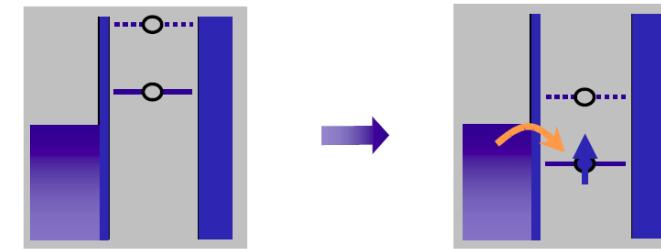
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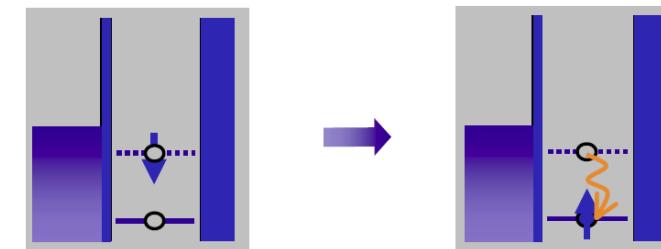


Initialization of a Single Electron Spin

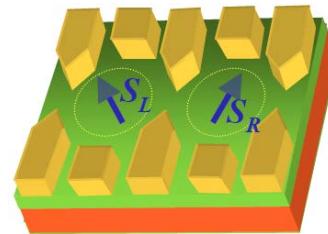
Method 1:
spin-selective tunneling



Method 2:
relaxation to ground state



Spin Qubits in Quantum Dots



Loss & DiVincenzo, *PRA* 1998
 Vandersypen et al., *Proc. MQC02* (quant-ph/0207059)

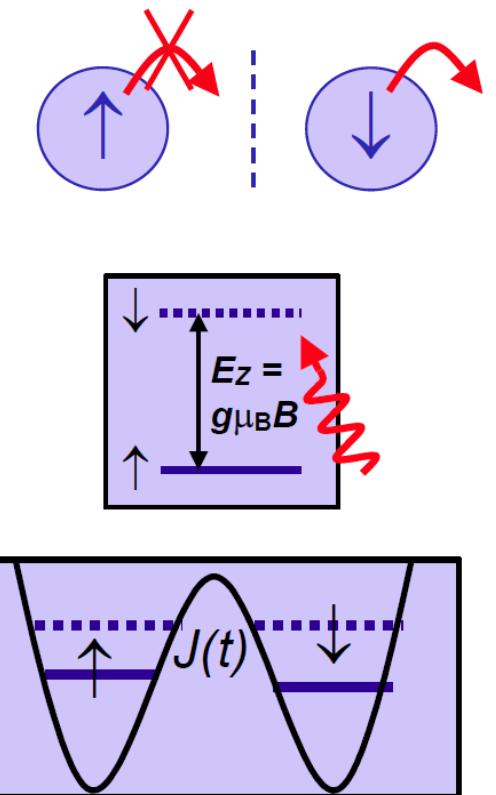
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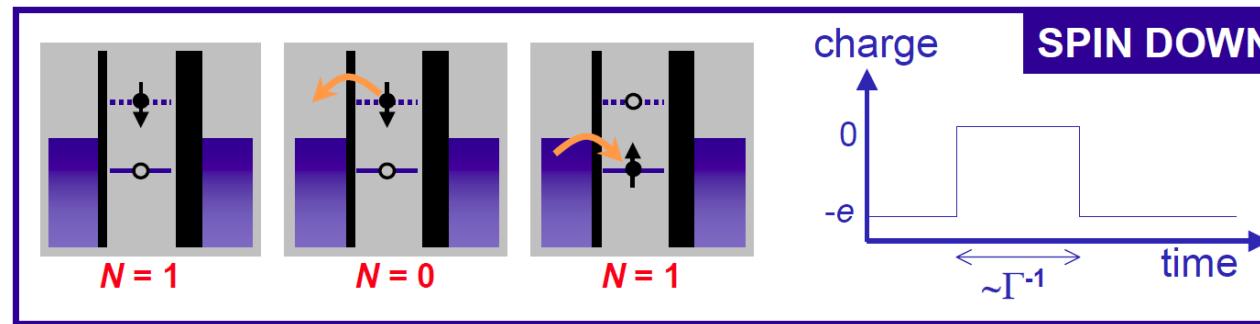
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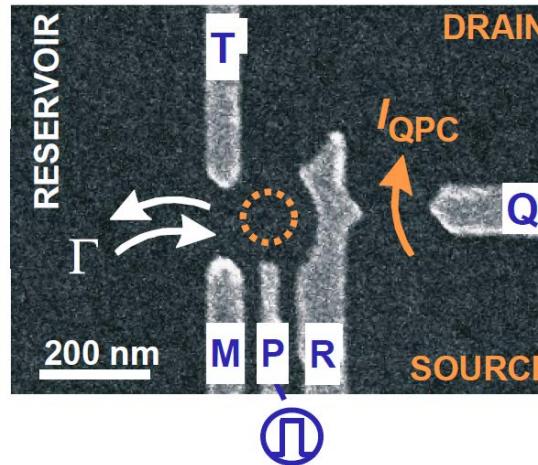
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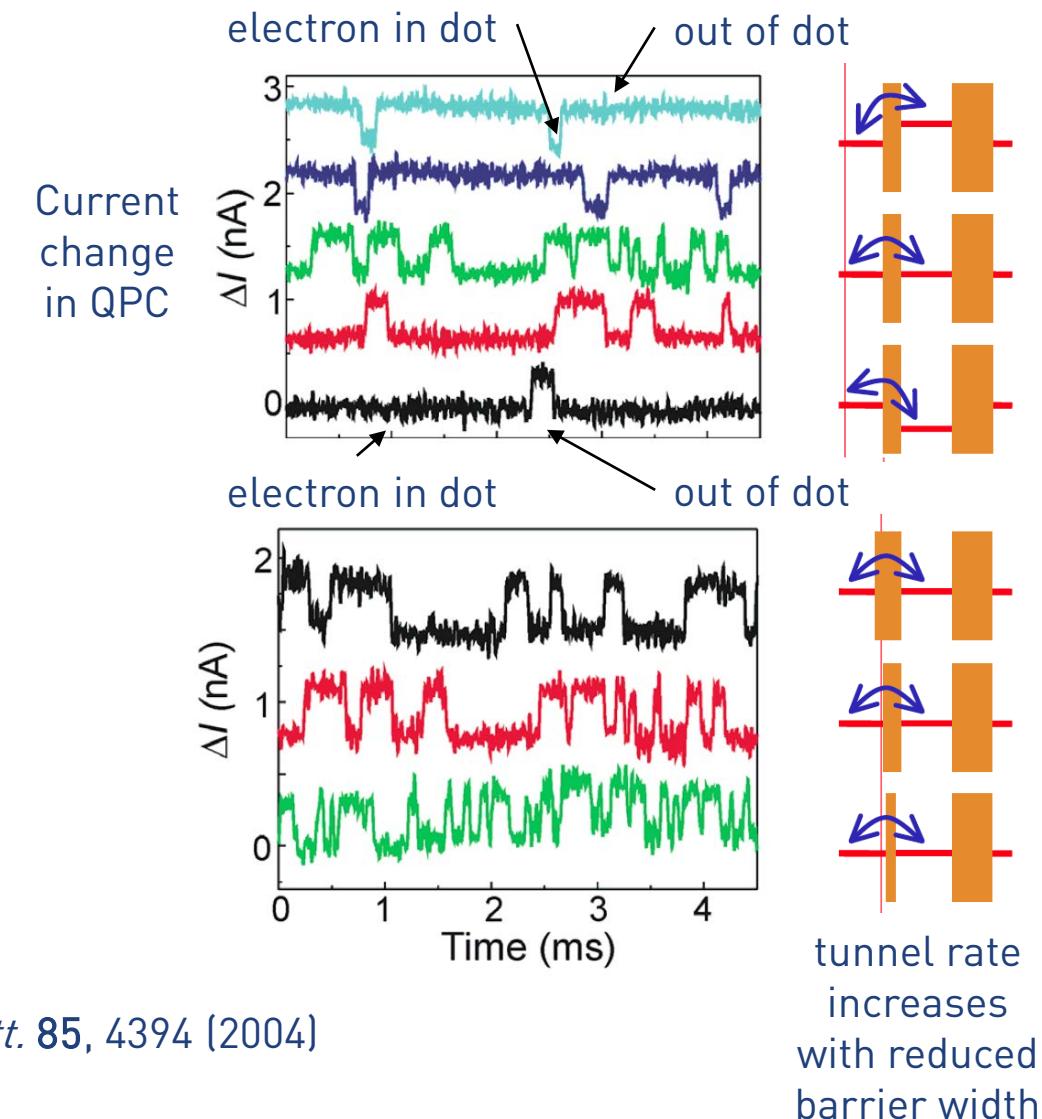
Spin Read-Out Principle: Convert Spin to Charge



Observation of individual tunnel events



- $V_{SD} = 1 \text{ mV}$
- $I_{QPC} \sim 30 \text{ nA}$
- $\Delta I_{QPC} \sim 0.3 \text{ nA}$
- Shortest steps $\sim 8 \mu\text{s}$

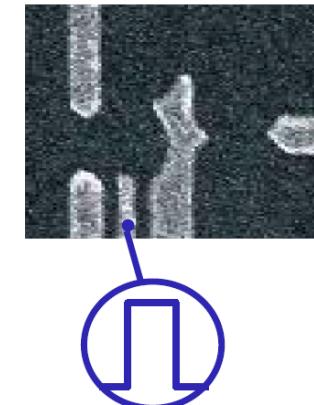
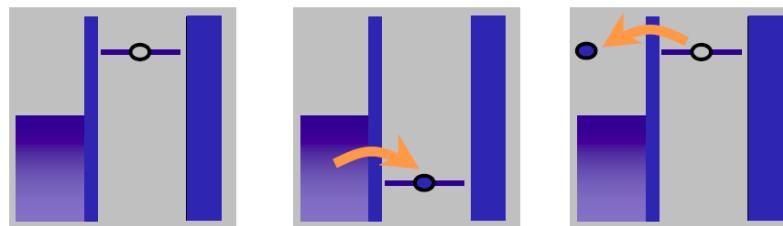
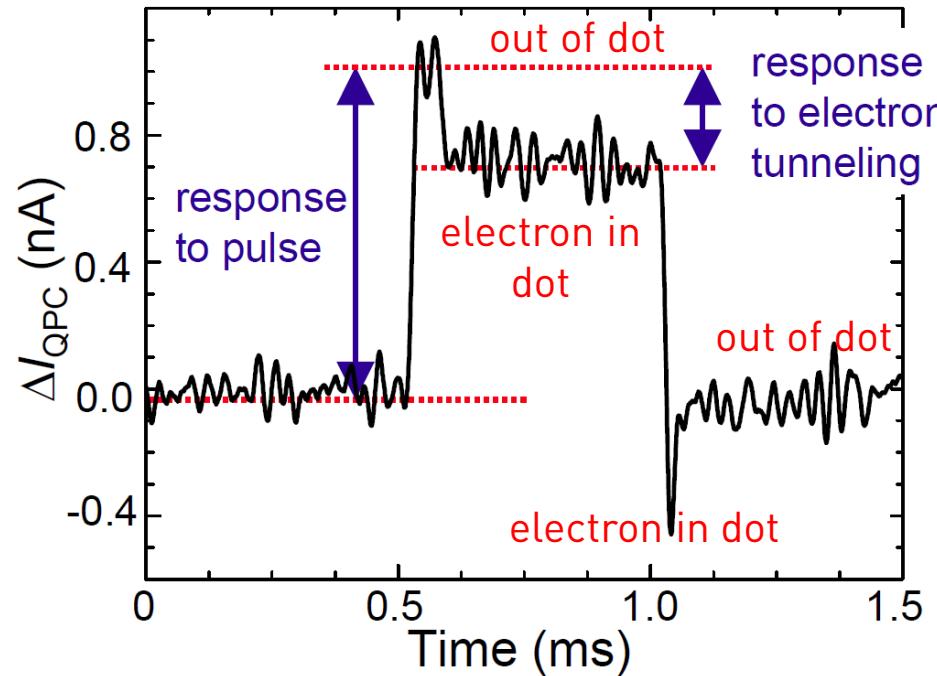


Vandersypen *et al.*, *App. Phys. Lett.* **85**, 4394 (2004)

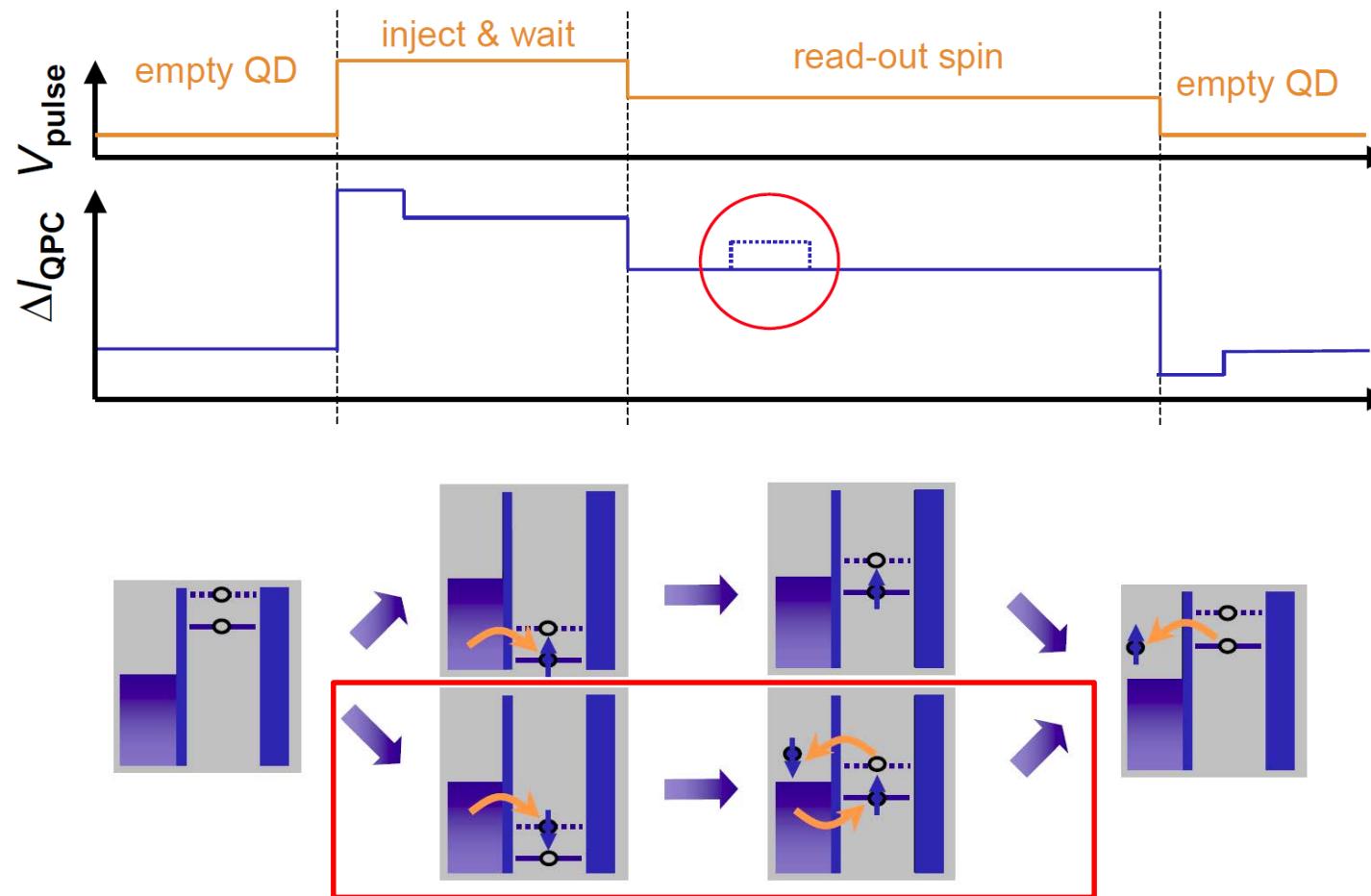
Schlessener *et al.*, (2004)

Slides and material courtesy of Lieven Vandersypen, TU Delft

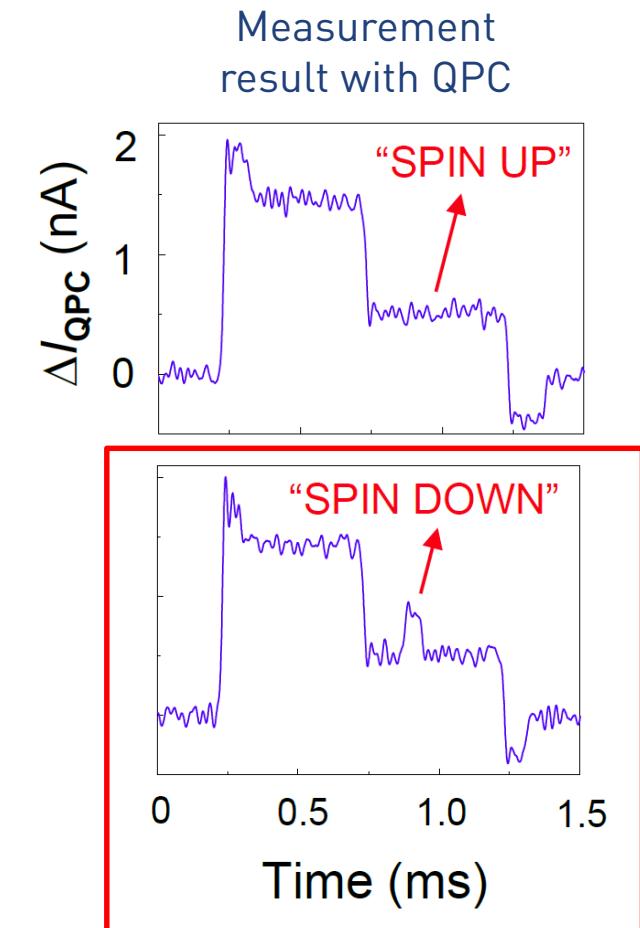
Pulse-Induced Tunneling



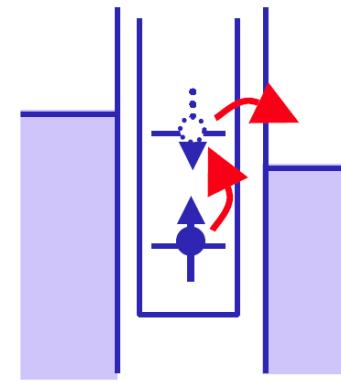
Spin Read-Out Procedure & Measurement Result



Inspiration: Fujisawa *et al.*, *Nature* **419**, 279 (2002)
 Elzerman *et al.*, *Nature* **430**, 431 (2004)
 Slides and material courtesy of Lieven Vandersypen, TU Delft



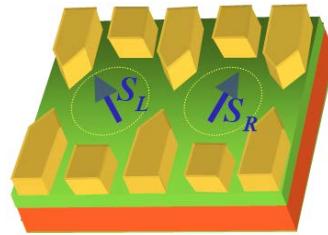
Electron Spin Resonance (ESR) Detection in a Single Dot



ESR lifts Coulomb blockade

Microwave induced spin flip raises (Zeeman) energy of electron and allows it to tunnel out to the right (drain) and new electron to tunnel in from the left (source) creating current.

Spin Qubits in Quantum Dots



Loss & DiVincenzo, *PRA* 1998
 Vandersypen et al., *Proc. MQC02* (quant-ph/0207059)

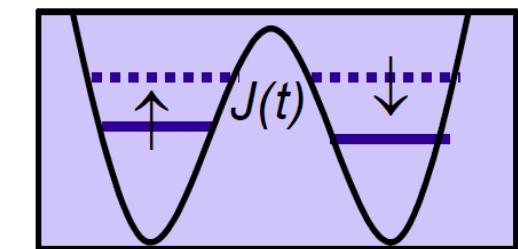
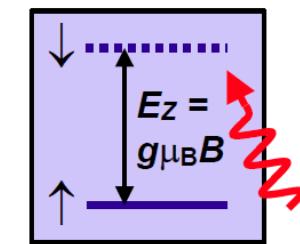
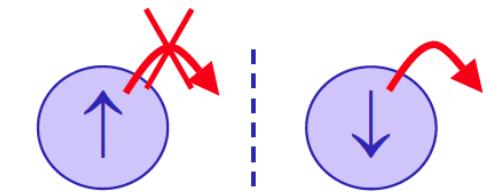
Initialization 1-electron, low T , high B_0
 $H_0 \sim \sum \omega_i \sigma_{zi}$

Read-out convert spin to charge
 then measure charge

ESR pulsed microwave magnetic field
 $H_{RF} \sim \sum A_i(t) \cos(\omega_i t) \sigma_{xi}$

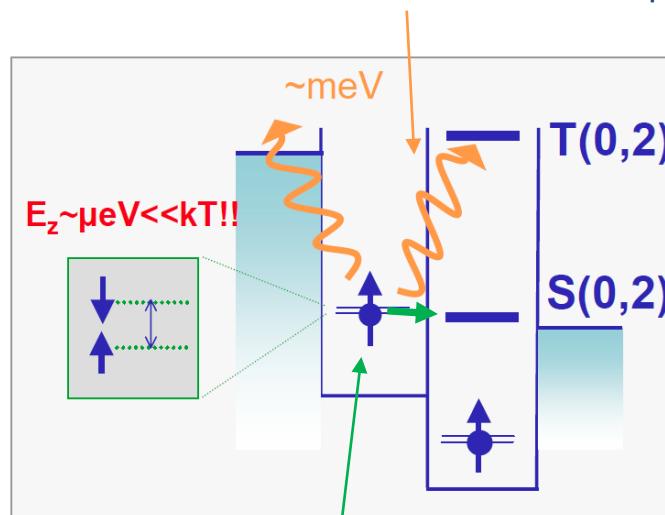
SWAP exchange interaction
 $H_J \sim \sum J_{ij}(t) \sigma_i \cdot \sigma_j$

Coherence long relaxation time T_1
 long coherence time T_2



Double Dot in Spin Blockade for ESR Detection

Tunneling of spin up from left to right is blockaded as it can only form triplet state (both spins up, $S=1$).



T: Triplet state
S: Singlet state

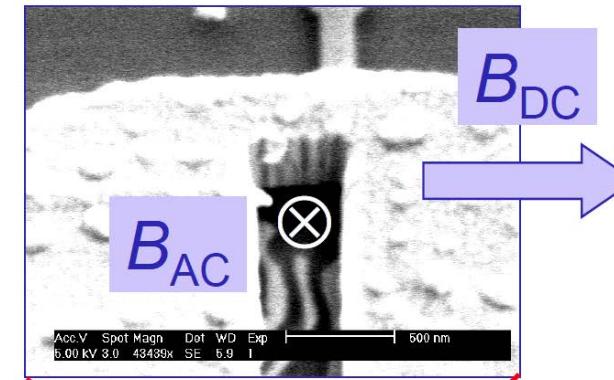
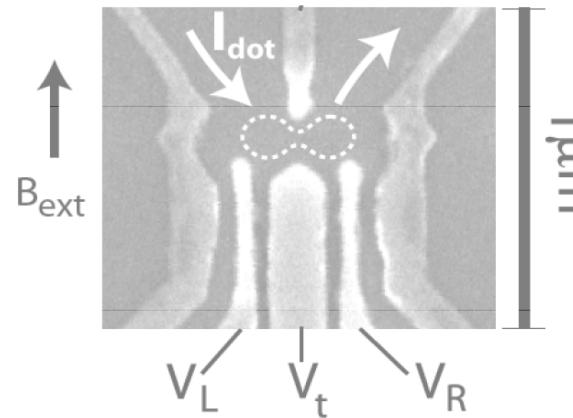
Advantage: inter-dot transition instead of dot-lead transition

- Insensitive to temperature
⇒ can use $B < 100 \text{ mT}$, $f < 500 \text{ MHz}$
- Insensitive to electric fields

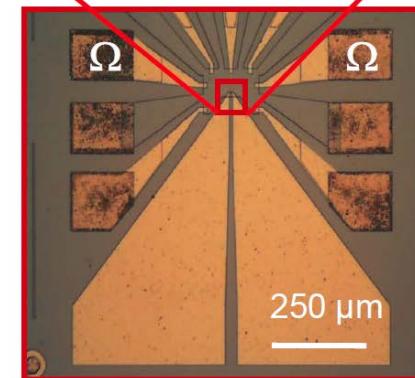
ESR spin flip (to down) allows for formation of lower energy singlet state (up and down $S=0$), lifts spin blockade and allows for tunneling from left to right creating current

Combine ESR detection: Engel & Loss, *Phys. Rev. Lett.* **86**, 4648 (2001)
with spin blockade: Ono & Tarucha, *Science* **297**, 1313 (2002)
Slides and material courtesy of Lieven Vandersypen, TU Delft

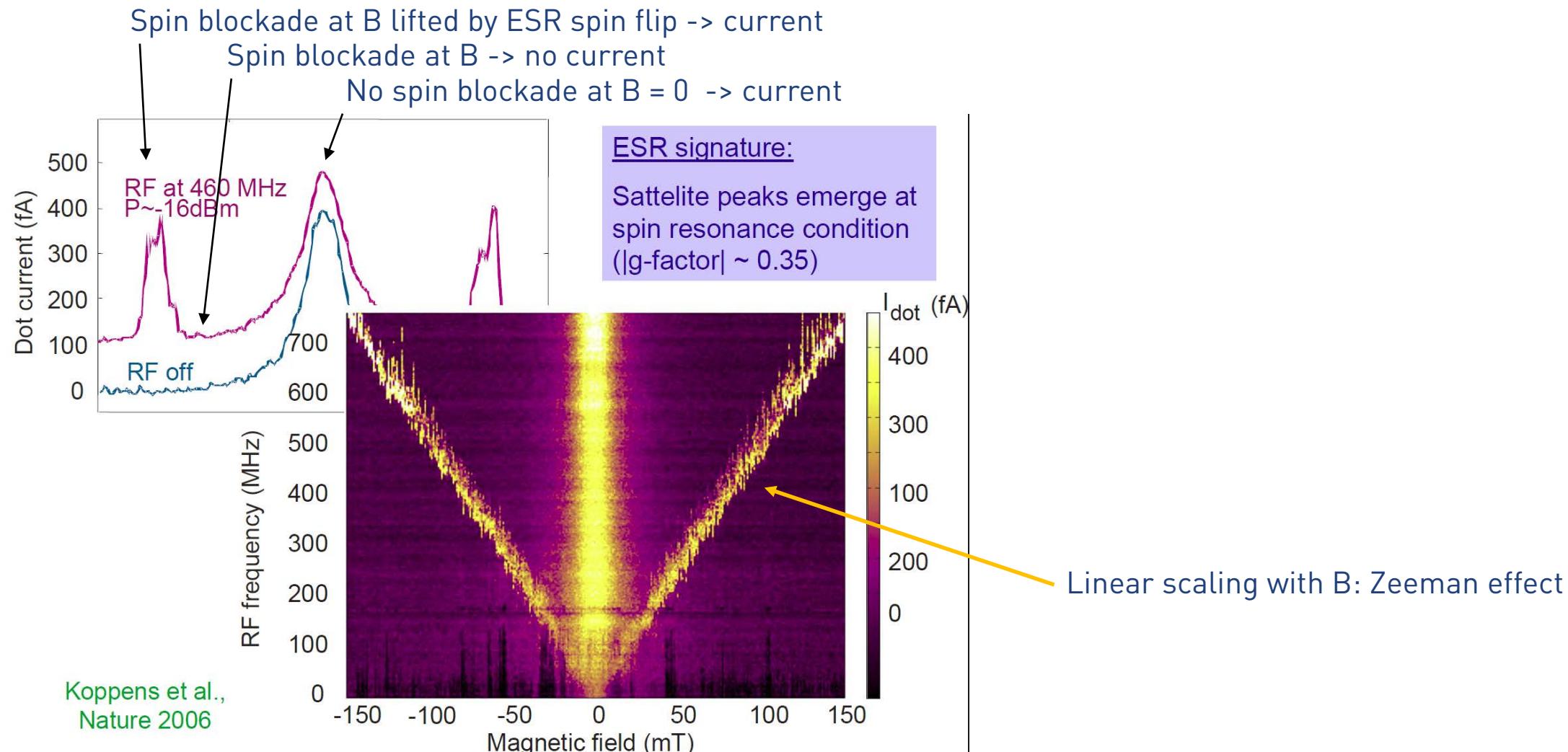
ESR Device Design



- Gates ~ 30 nm thick gold
- Dielectric ~ 100 nm calixerene
- stripline ~ 400 nm thick gold
- Expected AC current ~ 1 mA
- Expected AC field ~ 1 mT
- Maximize B_1 , minimize E_1



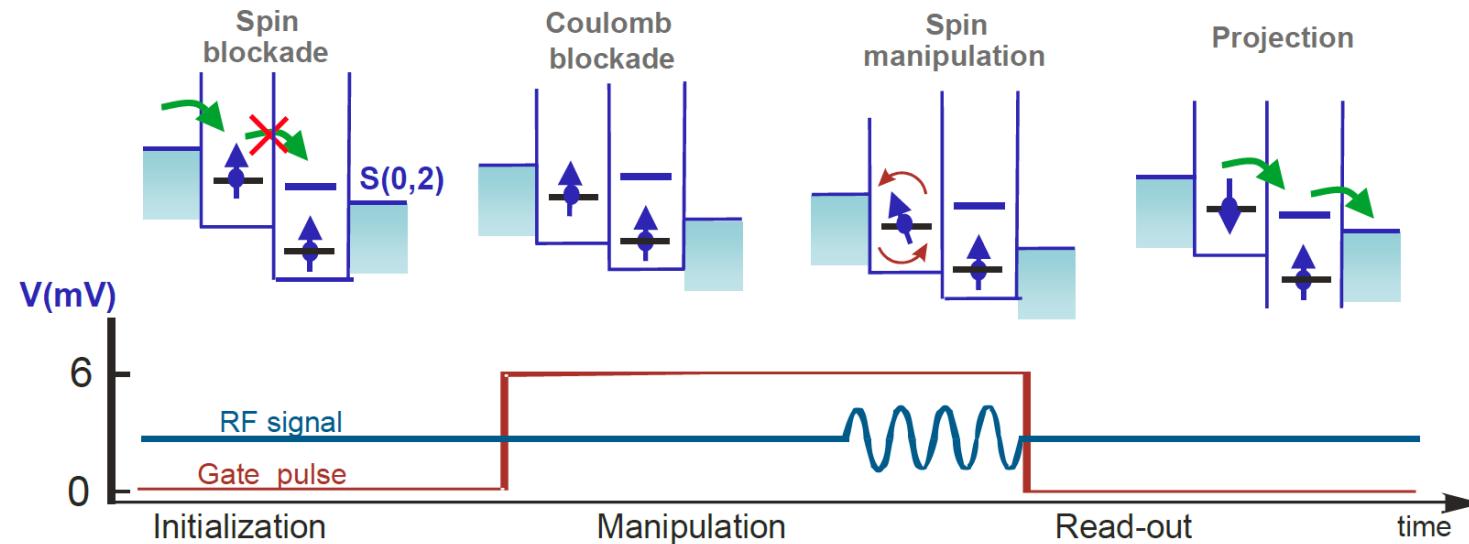
ESR Spin State Spectroscopy



Koppens *et al.*, Nature 442, 766 (2006)

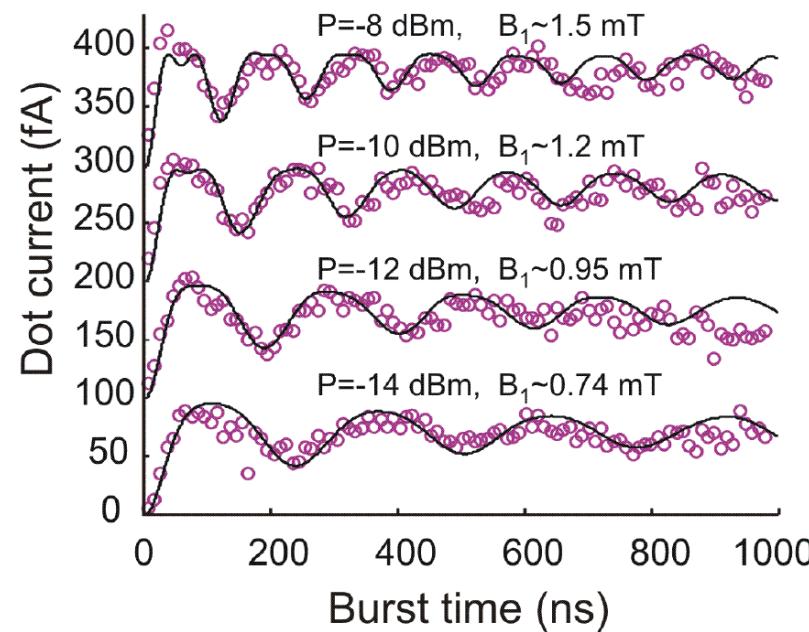
Slides and material courtesy of Lieven Vandersypen, TU Delft

Coherent Manipulation: Pulse Scheme



- Initialization in mixture of $\uparrow\uparrow$ and $\downarrow\downarrow$
- Measurement switched off (by pulsing to Coulomb blockade) during manipulation
- Read-out: projection on $\{\uparrow\uparrow, \downarrow\downarrow\}$ vs. $\{\uparrow\downarrow, \downarrow\uparrow\}$ basis

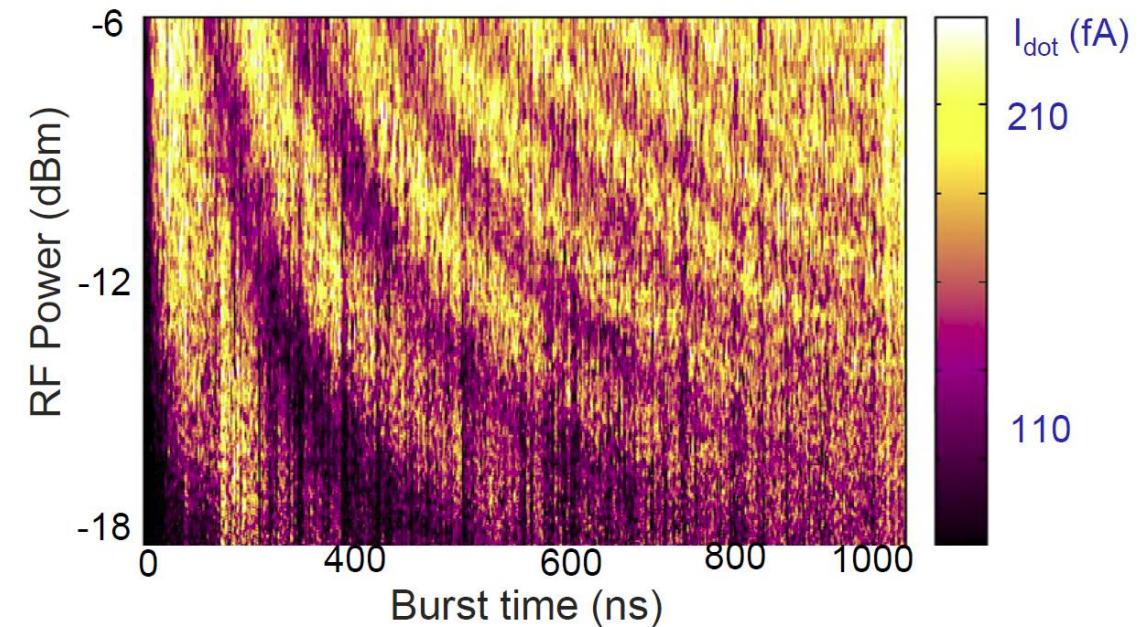
Coherent Rotations of Single Electron Spin



- Oscillations visible up to 1 μs
- Decay non exponential
 - slow nuclear dynamics (non-Markovian bath)
- Agreement with simple Hamiltonian
- Taking into account different resonance conditions both dots

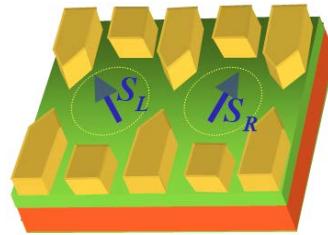
Koppens *et al.*, *Nature* **442**, 766 (2006)

Slides and material courtesy of Lieven Vandersypen, TU Delft



- Oscillation frequency $\sim B_{\text{AC}}$
 - clear signature of Rabi oscillations
- $\pi/2$ pulse in 25 ns
- max $B_1 = B_{\text{AC}}/2 = 1.9 \text{ mT}$
- $B_{N,z} = 1.3 \text{ mT}$
 - estimated fidelity $\sim 73\%$

Spin Qubits in Quantum Dots



Loss & DiVincenzo, *PRA* 1998
 Vandersypen et al., *Proc. MQC02* (quant-ph/0207059)

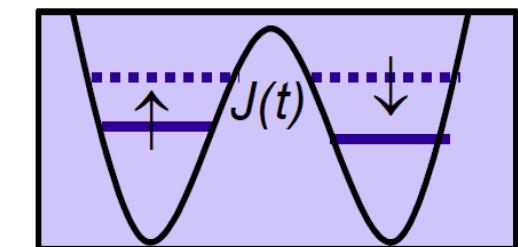
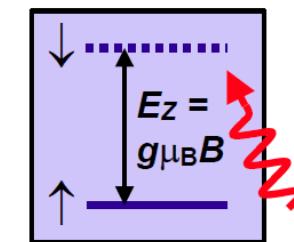
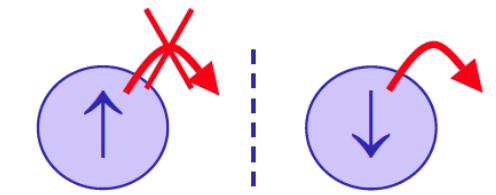
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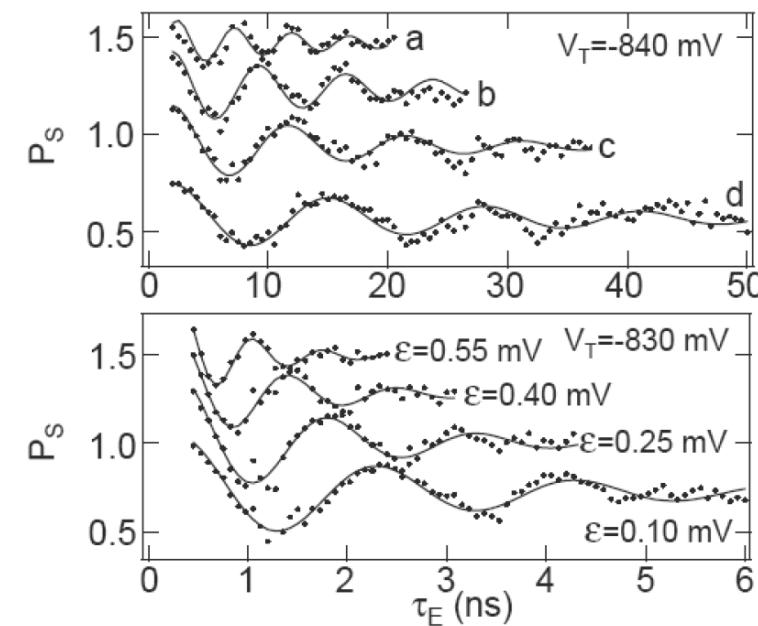
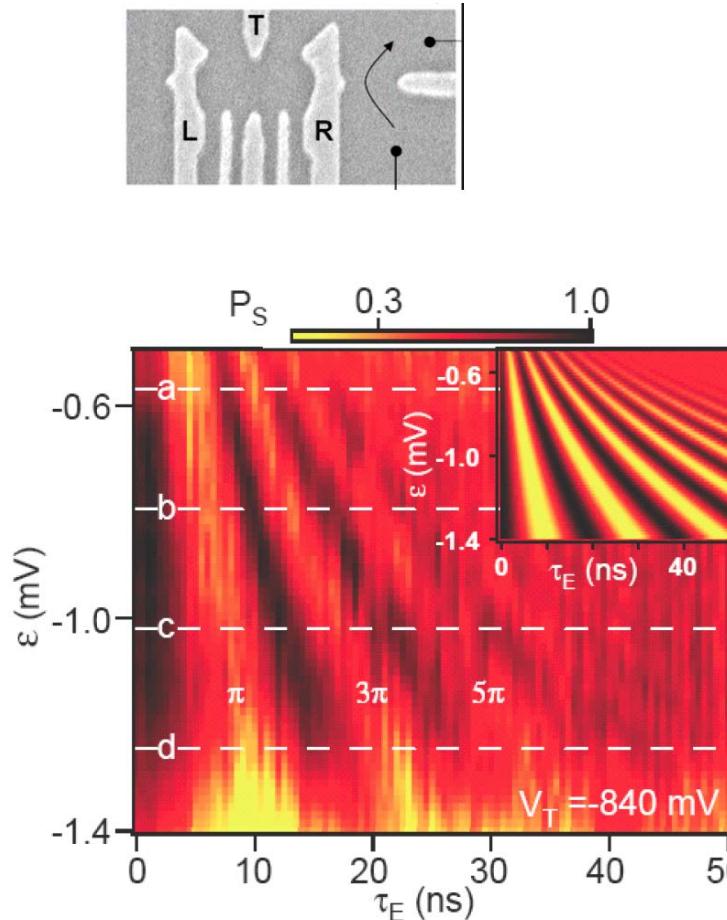
ESR pulsed microwave magnetic field
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SWAP exchange interaction
 $H_J \sim \sum J_{ij}(t) \sigma_i \cdot \sigma_j$

Coherence long relaxation time T_1
 long coherence time T_2



Coherent Exchange of Two Spins



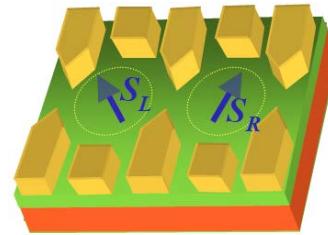
Petta *et al.*, *Science* **309**, 2180 (2005)

Slides and material courtesy of Lieven Vandersypen, TU Delft

Spin exchange as in NMR

- free evolution under exchange Hamiltonian
- swap $^{1/2}$ in as little as 180 ps
- three oscillations visible, independent of J

Spin Qubits in Quantum Dots



Loss & DiVincenzo, *PRA* 1998
Vandersypen et al., *Proc. MQC02* (quant-ph/0207059)

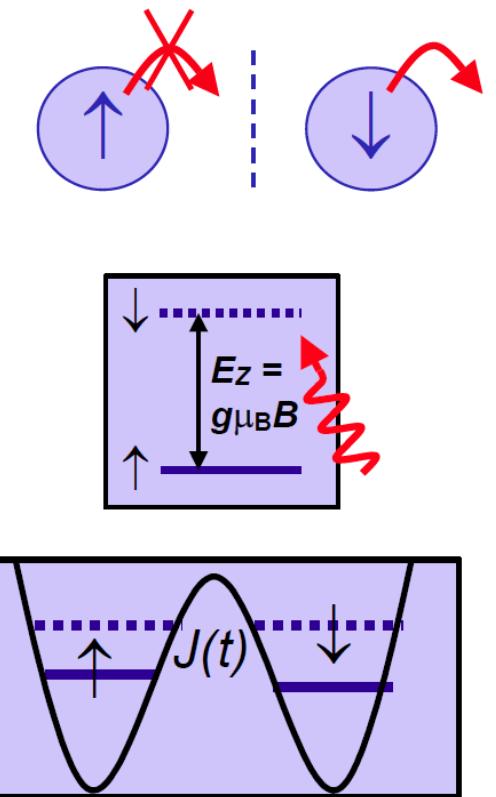
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SWAP exchange interaction
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Coherence long relaxation time T_1
long coherence time T_2



Summary Gate-Defined Quantum Dots

Semiconductor quantum dots for QIP

- Fulfill all DiVincenzo Criteria

Challenges

- Use materials with long spin lifetimes (Si, graphene) and low charge noise
- Scaling to larger number of qubits

Current promising developments

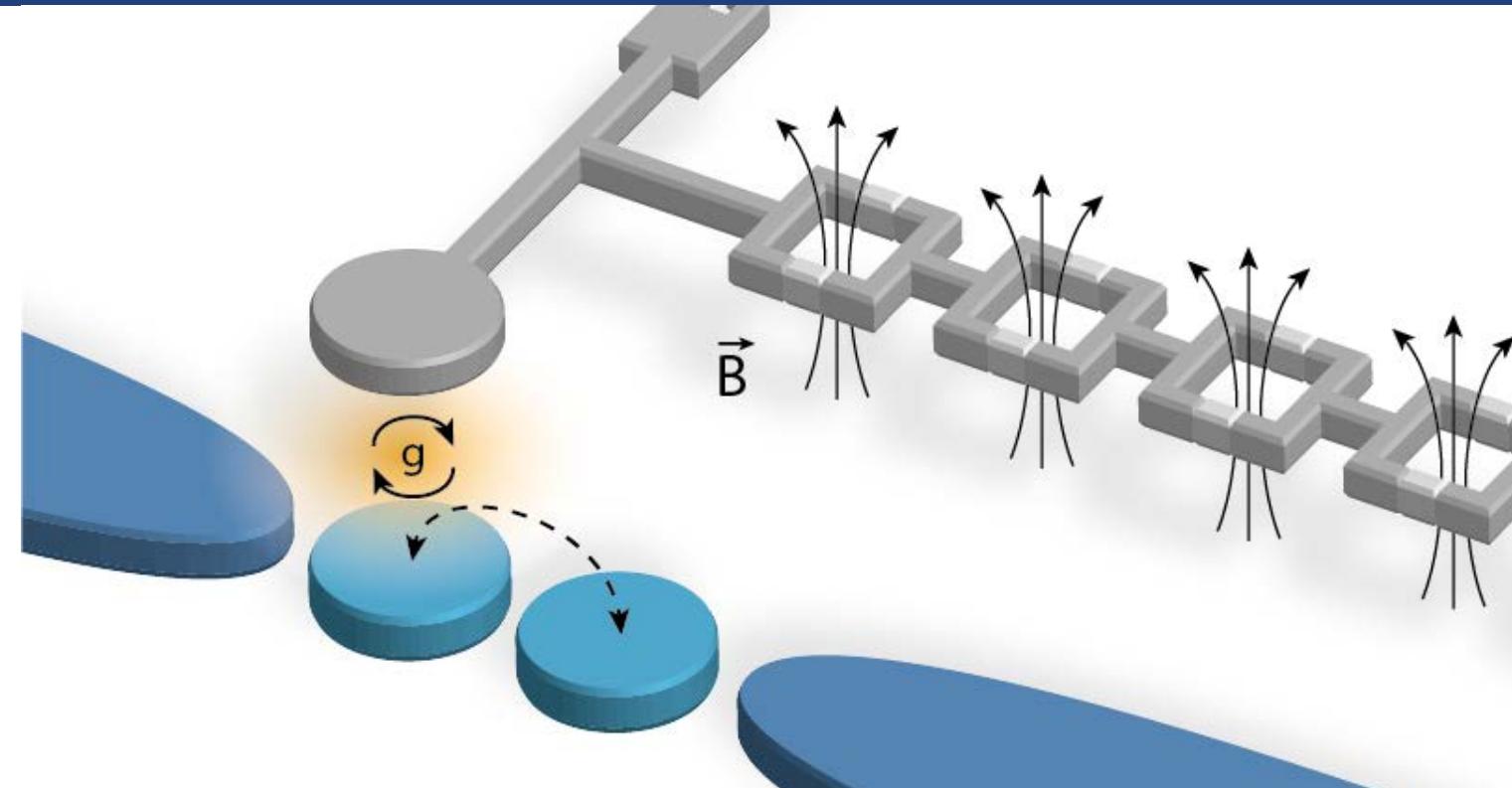
- Circuit QED for quantum dots
(see additional slides)

Book on basics:

- Thomas Ihn, Semiconductor Nanostructures: Quantum States and Electronic Transport, ISBN 978-0-19-953442-5, Oxford University Press, Oxford, 2010.

Introductory Review Articles:

- R. Hanson, L. P. Kouwenhoven, J. R. Petta et al., Spins in few-electron quantum dots, *Reviews of Modern Physics* **79**, 1217 (2007)
- R. Hanson, & D. D. Awschalom, Coherent manipulation of single spins in semiconductors, *Nature* **453**, 1043 (2008)

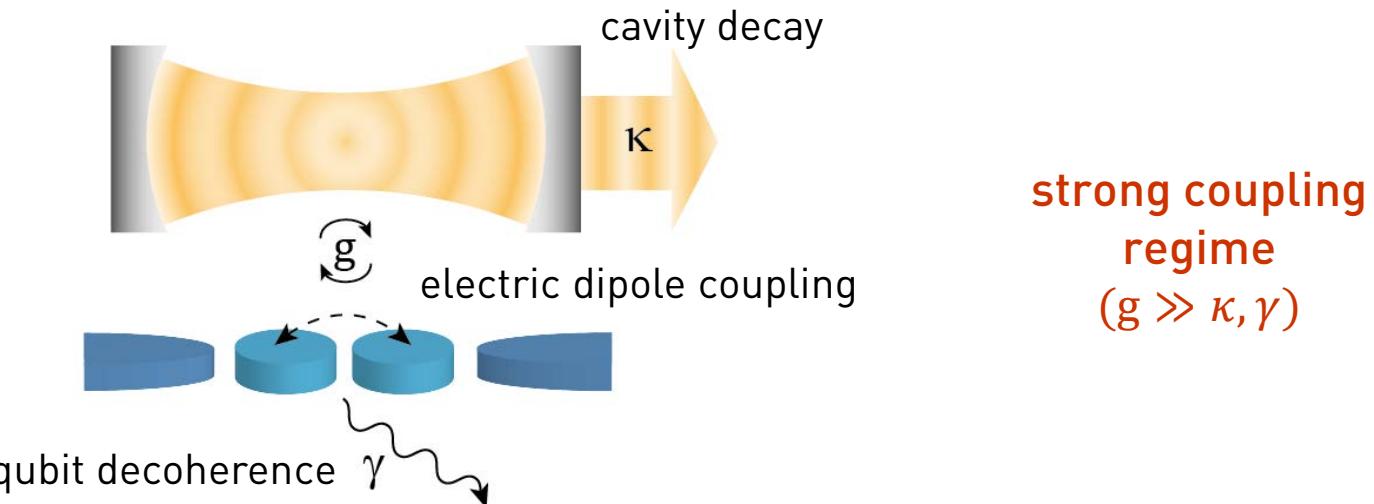


Strong Coupling Cavity QED with Semiconductor Quantum Dots Enabled by High Impedance SQUID Array Resonators

A. Stockklauser, P. Scarlino, J. V. Koski, S. Gasparinetti, C. K. Andersen, C. Reichl, W. Wegscheider, T. Ihn,
K. Ensslin, A. Wallraff (ETH Zurich)

Development of Circuit QED for Semiconductor Quantum Dots

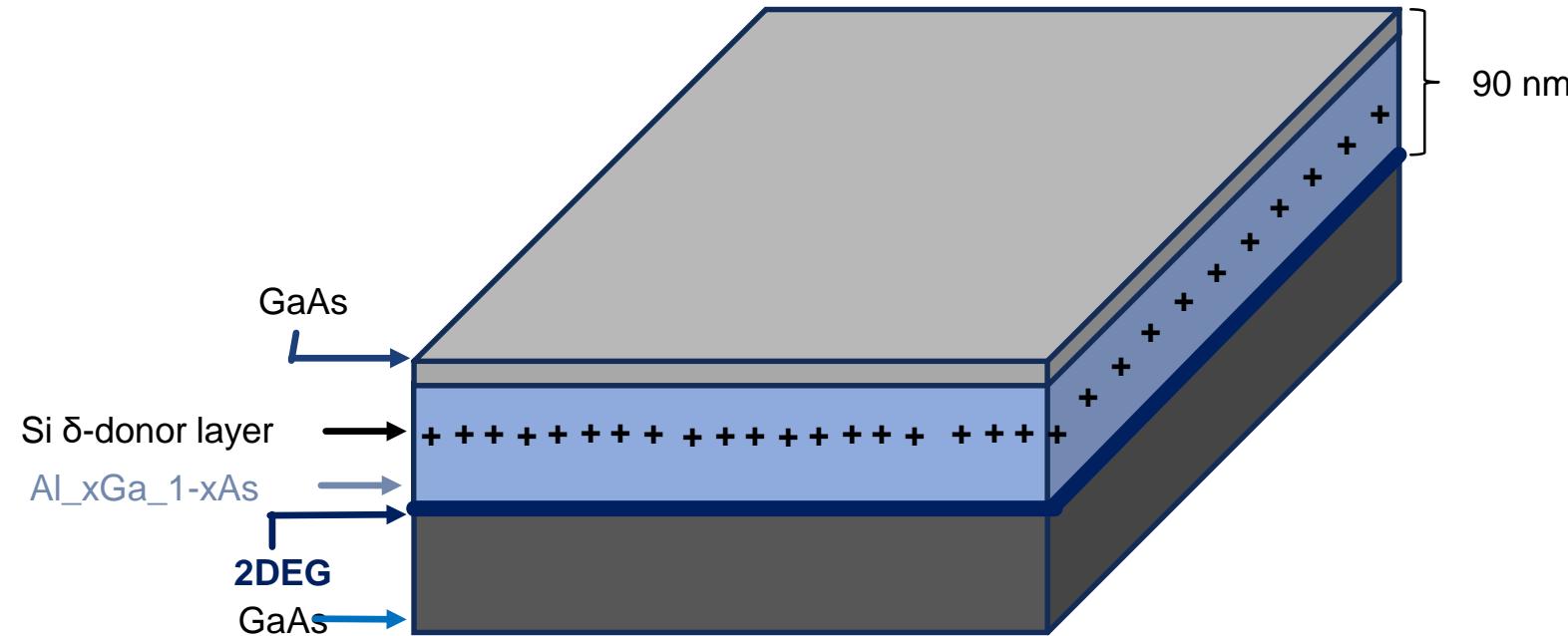
Microwave cavities



Semiconductor quantum dots

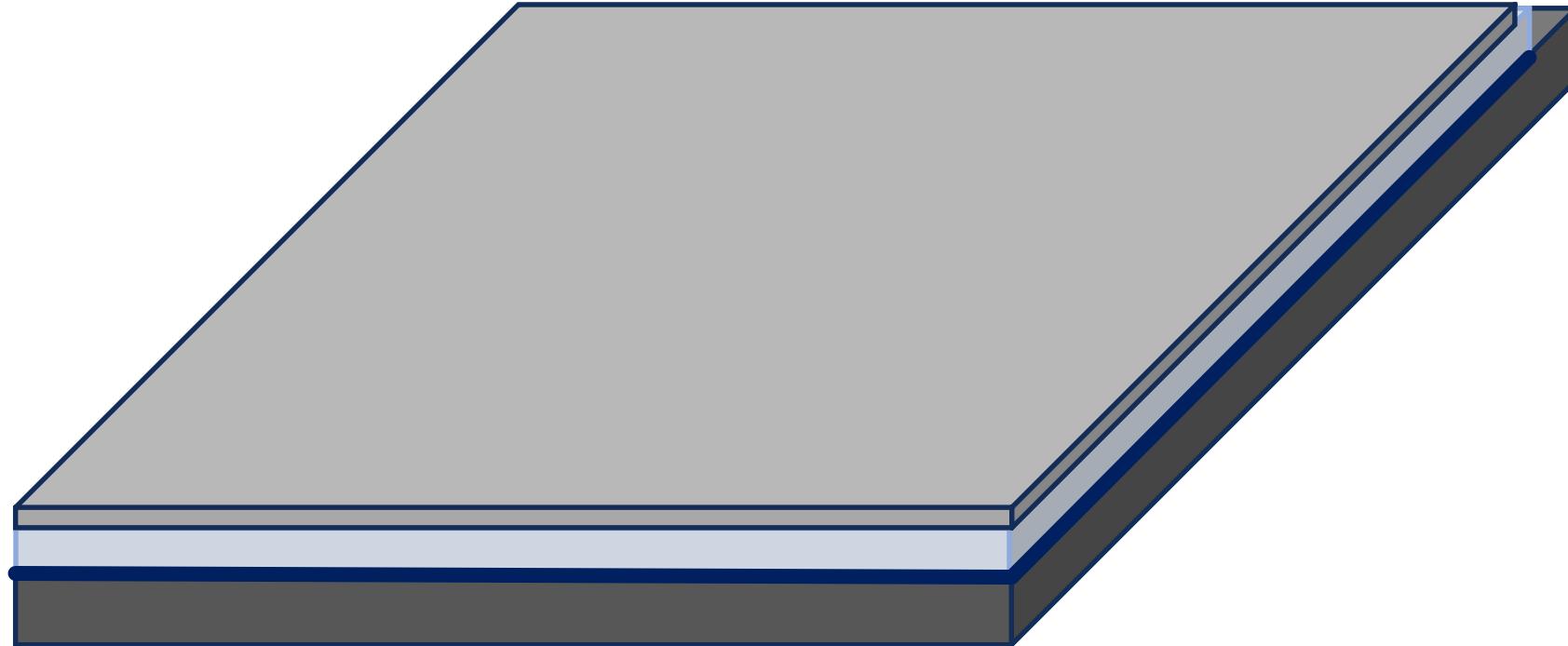
	$\gamma/2\pi$	$g/2\pi$	
■ GaAs DQDs Frey <i>et al.</i> , <i>PRL</i> 108 , 046807 (2012) Toida <i>et al.</i> , <i>PRL</i> 110 , 066802 (2013)	300 MHz	30-50 MHz	not in the strong coupling regime ($g \ll \gamma$)
■ InAs nanowire DQDs Petersson <i>et al.</i> , <i>Nature</i> 490 , 380-383 (2012)	1 GHz	20-50 MHz	
■ Carbon nanotube DQDs Delbecq <i>et al.</i> , <i>PRL</i> 107 , 256804 (2011)			
■ Graphene DQDs Deng <i>et al.</i> , <i>PRL</i> 115 , 126804 (2015)			

Double Quantum Dots Created in GaAs Heterostructure

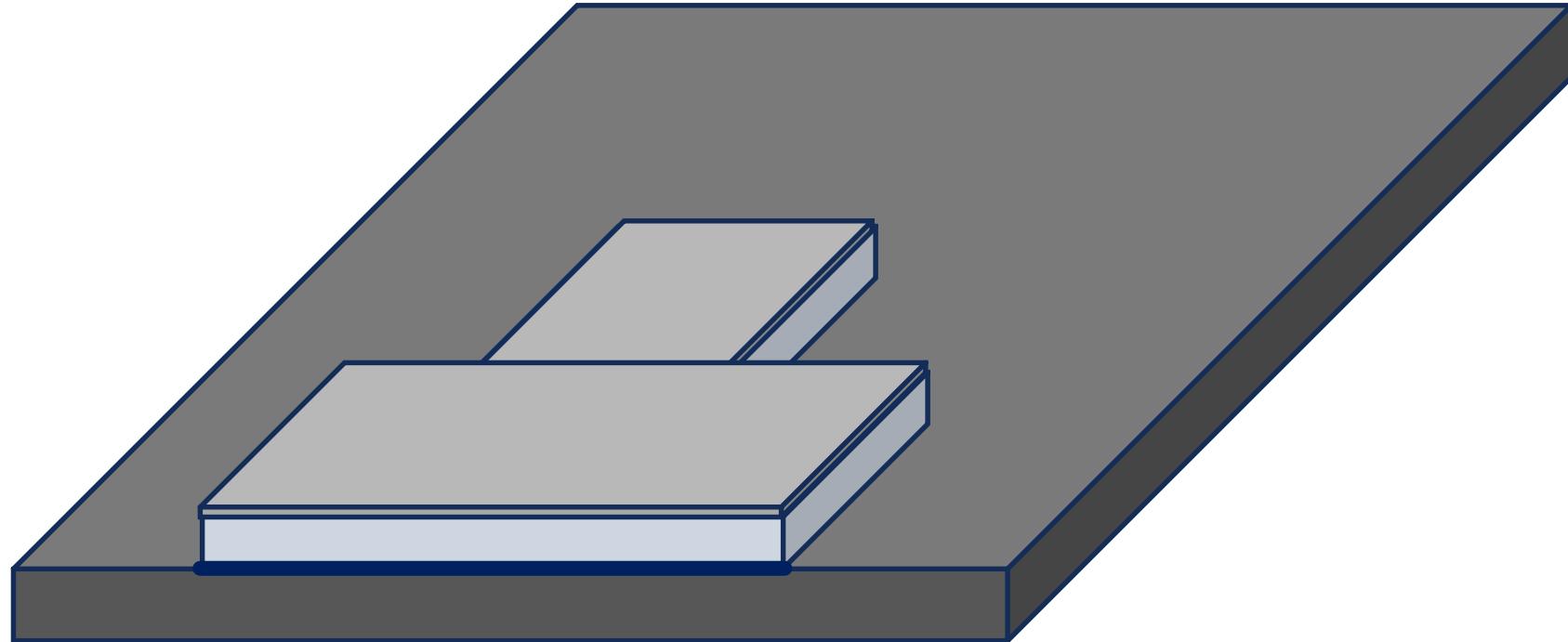


Wafer : C. Reichl, W. Wegscheider

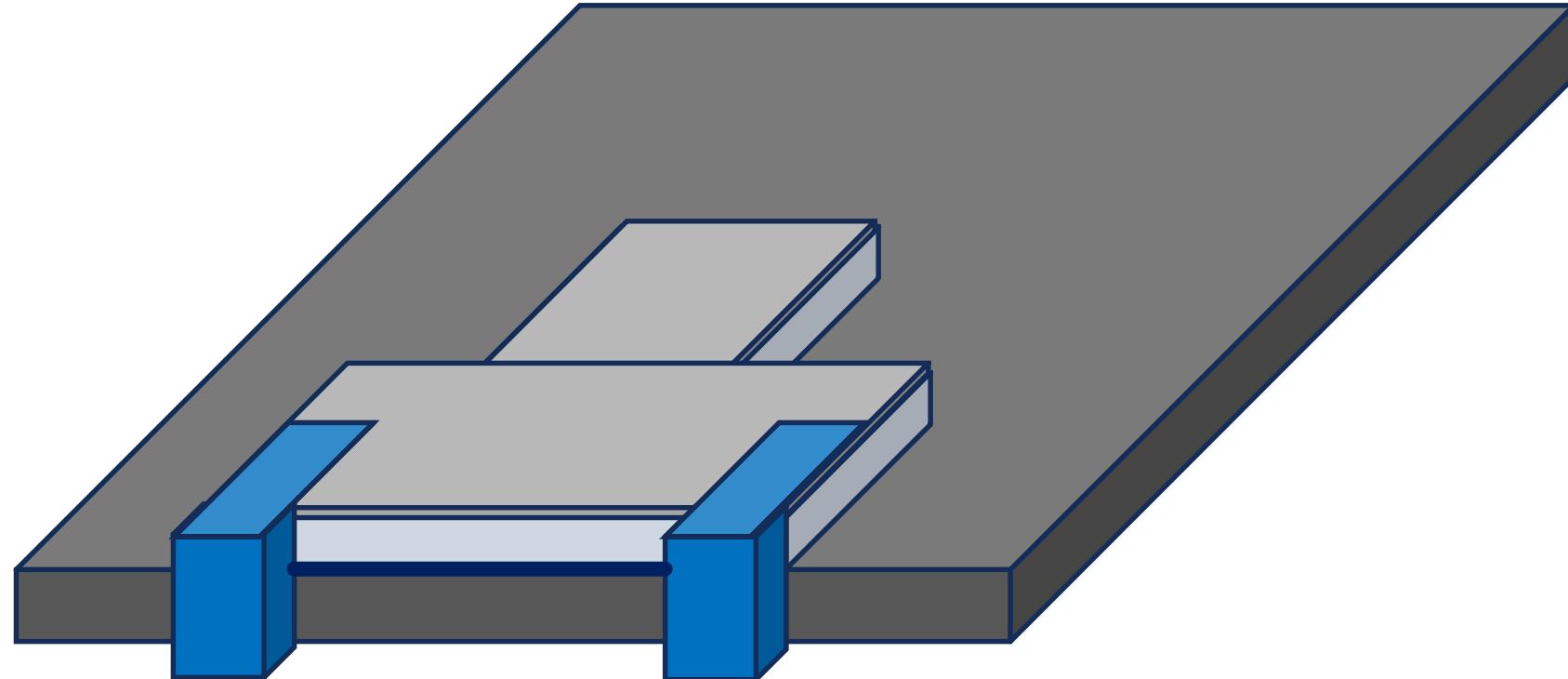
GaAs/AlGaAs Heterostructure



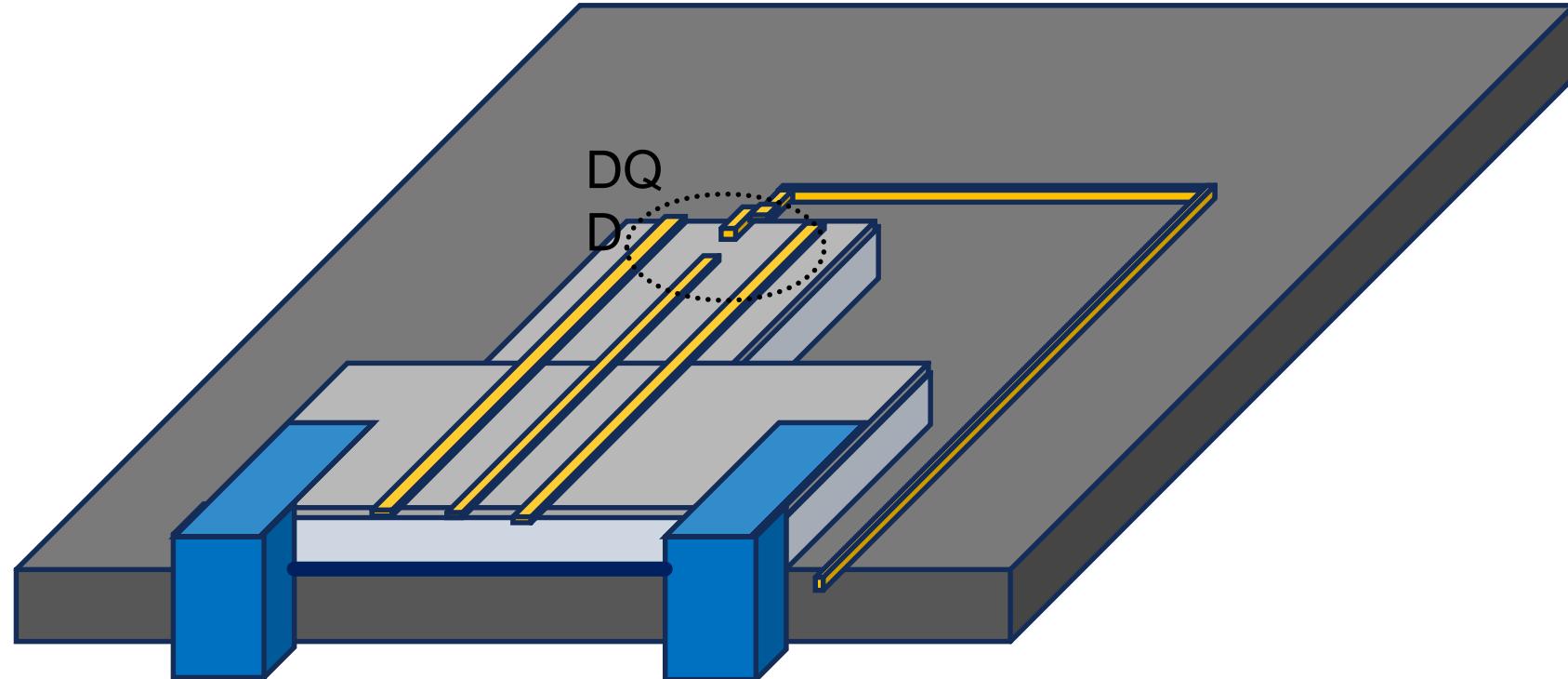
MESA Etching



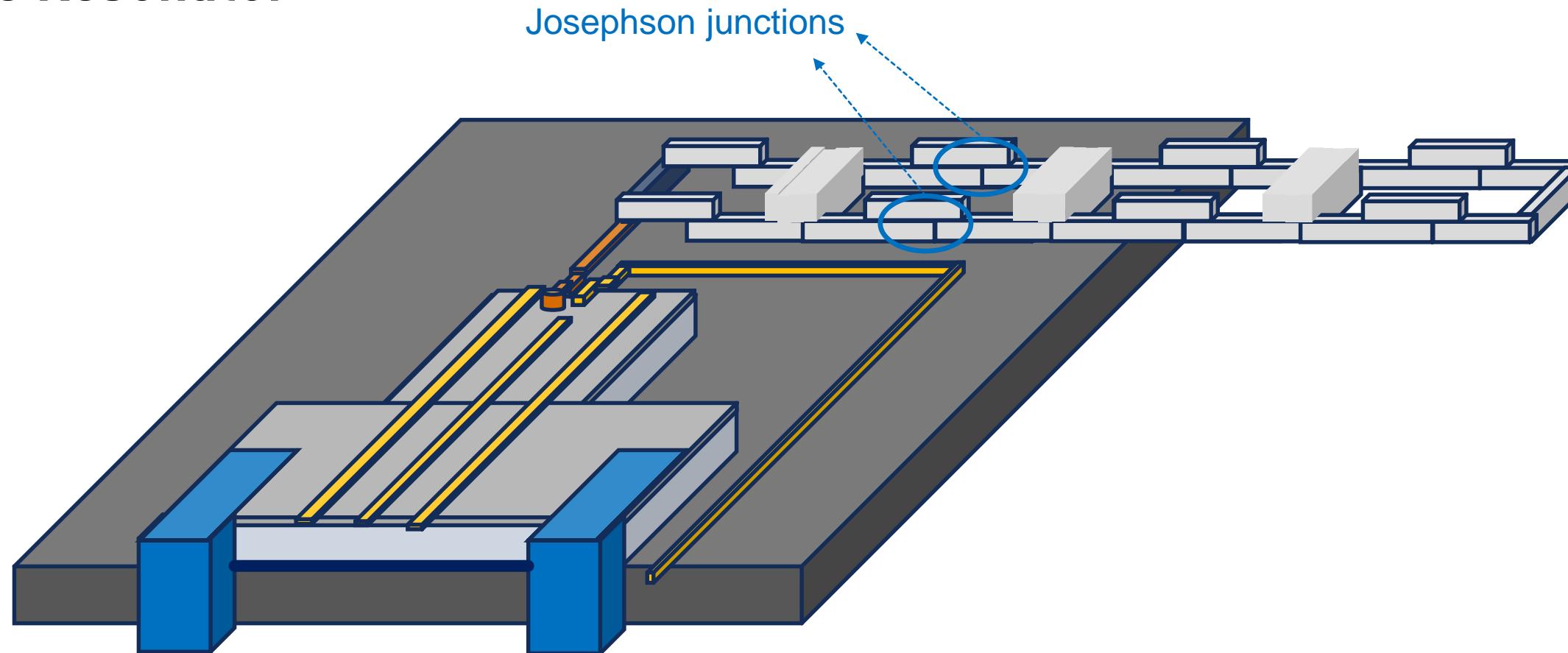
Ohmic Contacts



Depletion Gates



Microwave Resonator



High Impedance SQUID Array Resonator

- Increase dipole coupling

$$g \propto d \cdot V_0^{\text{rms}} \propto \omega_r \sqrt{Z_r}$$

- Maximize impedance $Z_r = \sqrt{L_r/C_r}$
- Josephson junction as high impedance circuit elements

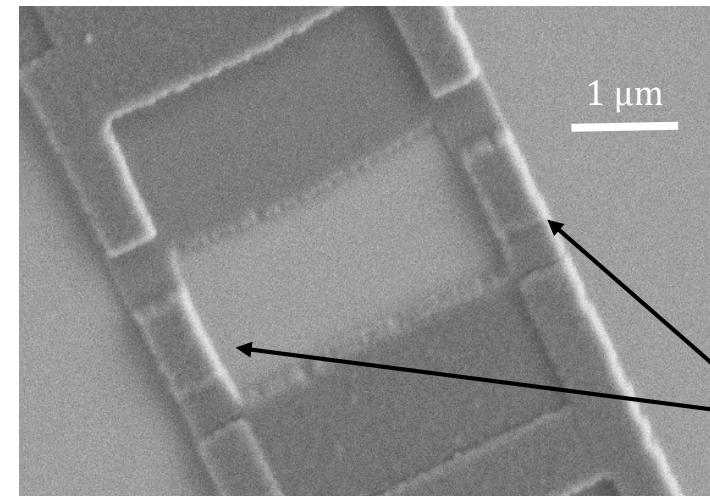
$$L_J = \frac{\Phi_0}{2\pi I_c \cos \varphi_0}$$

→ Resonator design based on SQUID array

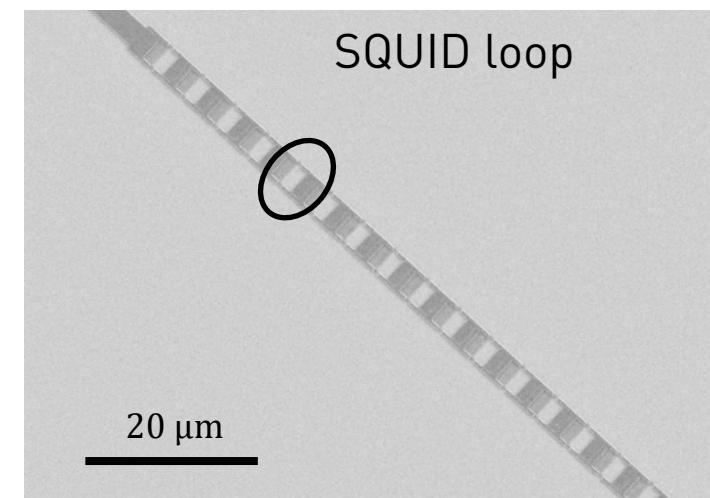
Altimiras et al., APL 103, 212601 (2013).

Masluk et al., PRL 109, 137002 (2012).

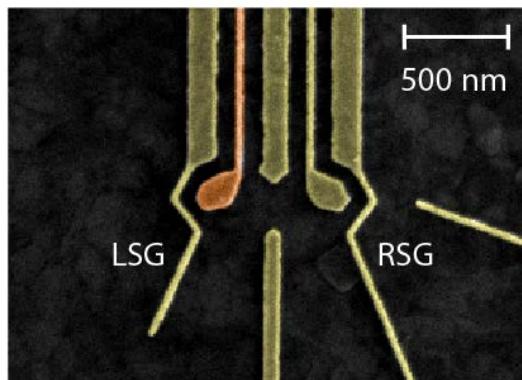
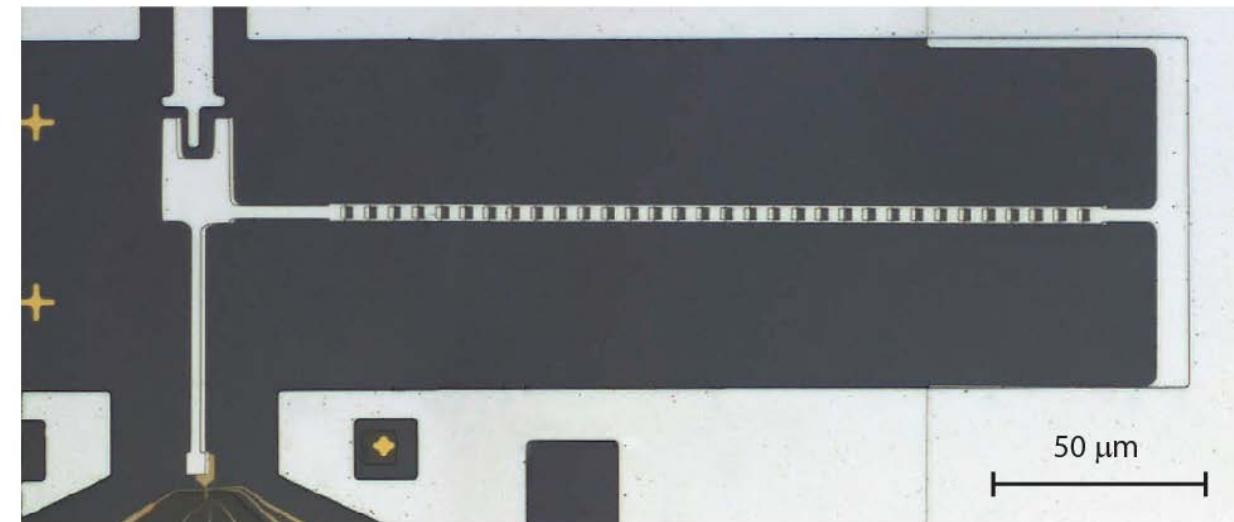
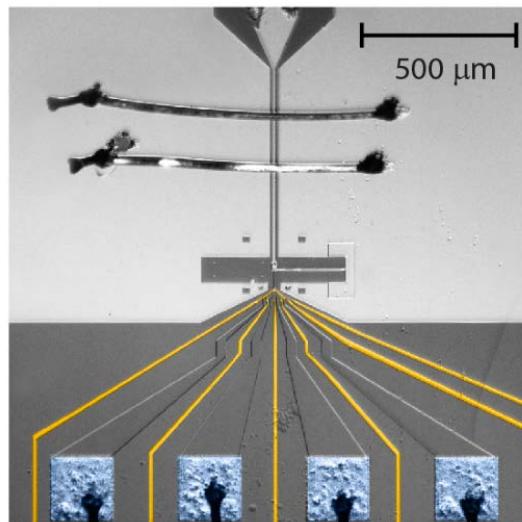
Castellanos-Beltran, Lehnert, APL 91, 083509 (2007).



Josephson
junctions

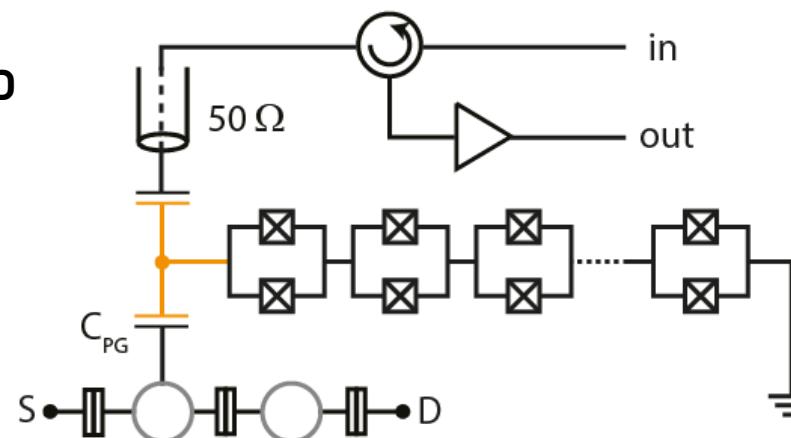


Integrated GaAs DQD with SQUID Array Resonator in Hybrid Device



Gate defined GaAs DQD

- On small mesa
- Resonator coupling gate not DC biased



32 SQUID array resonator

- 200 μm long
- Al based
- Dolan bridge technique

Microwave reflectometry measurement

- Josephson parametric amplifier
- Custom FPGA electronics

Characteristics of SQUID Array Resonator

- SQUID inductance

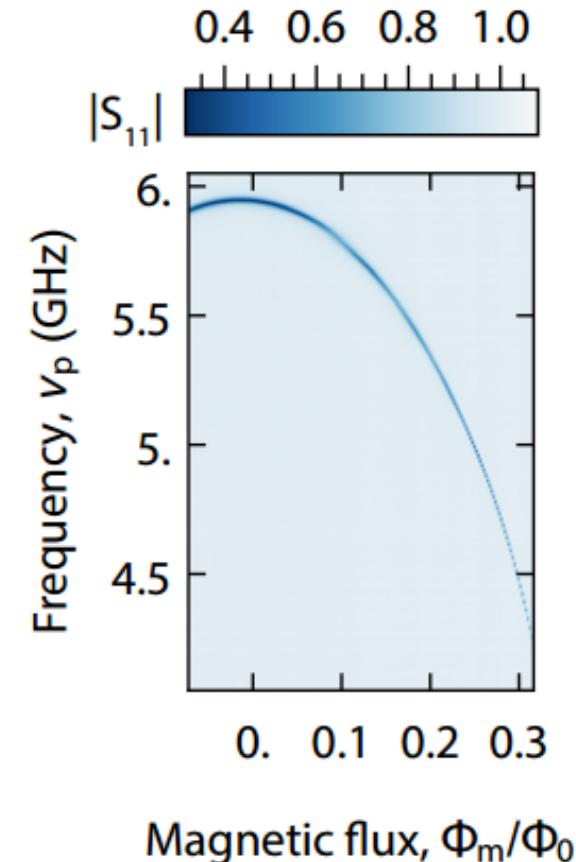
$$L_J^S(\Phi_m) \propto |\cos\left(\frac{\pi\Phi_m}{\Phi_0}\right)|^{-1}$$

→ Flux-tunable inductance, impedance and resonance frequency

- $\nu_r = 4 - 6 \text{ GHz}$
- $Z_r = 1.3 - 1.8 \text{ k}\Omega$

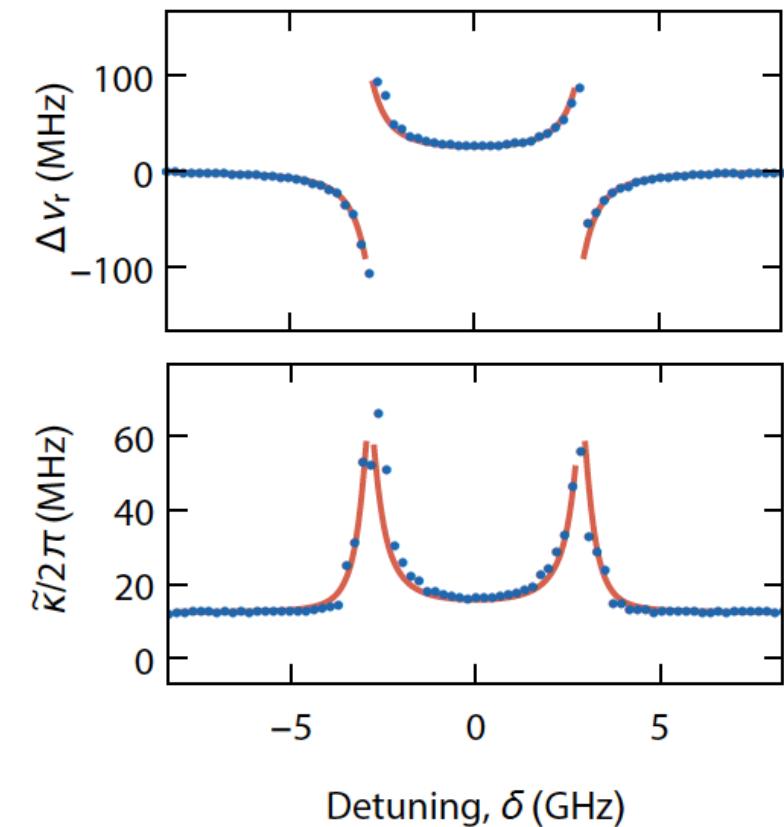
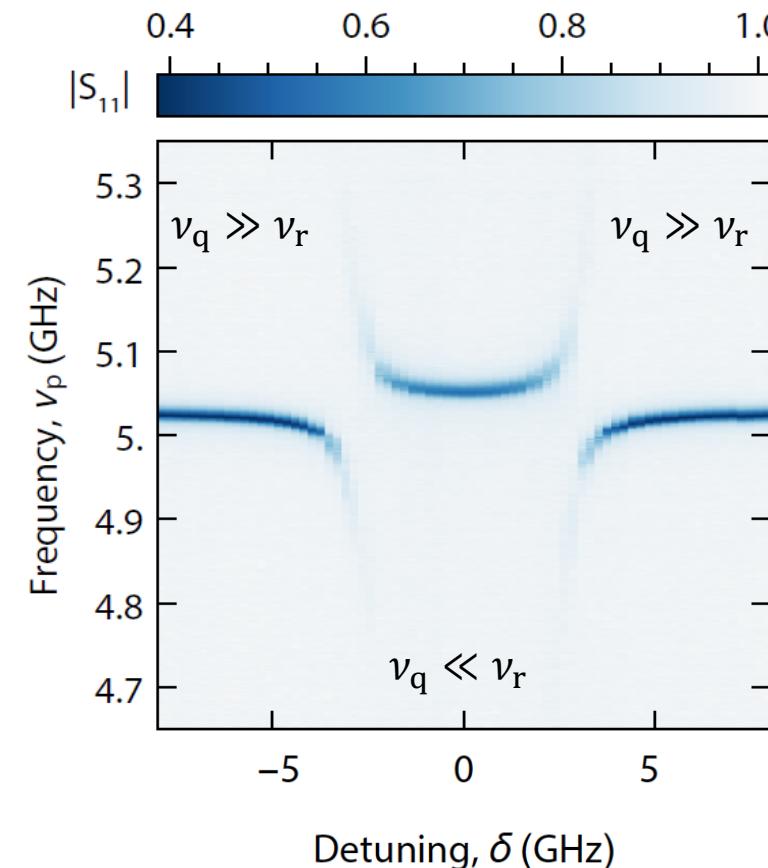
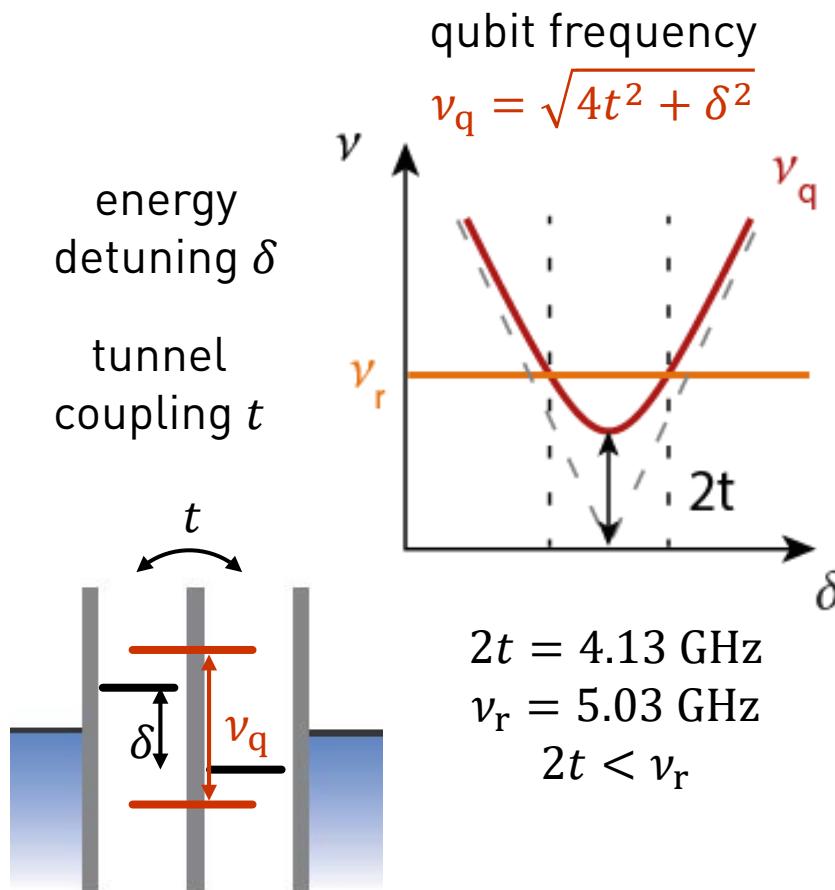
$$\rightarrow \sqrt{Z_r / 50 \Omega} \sim 6$$

- $(\kappa_{\text{int}}, \kappa_{\text{ext}}, \kappa) / 2\pi = (10.0, 2.3, 12.3) \text{ MHz}$



Stockklauser, Scarlino *et al.*, PRX7, 011030 (2017)

Dispersive Interaction



Dispersive indication of strong coupling: $(g, \gamma_1, \gamma_\varphi, \kappa)/(2\pi) = (145, 60, 38, 12) \text{ MHz}$

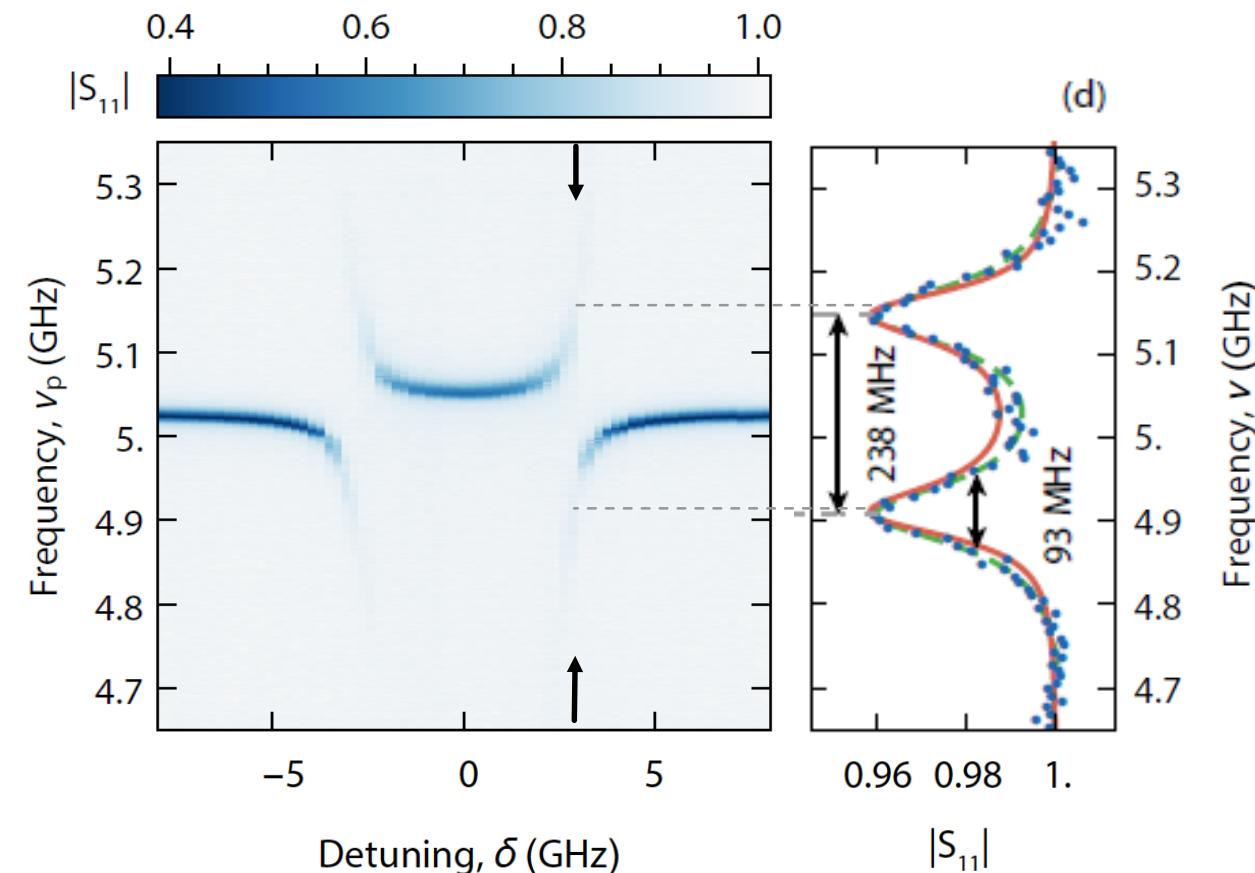
Strong Resonant Interaction

First (joint with Petta at Princeton) observation of **strong coupling cavity QED ($g > \kappa, \gamma$)** in **gate defined semiconductor QDs**:

$$\begin{aligned} (g, \gamma_1, \gamma_\varphi, \kappa)/(2\pi) \\ = (145, 60, 38, 12) \text{ MHz} \end{aligned}$$

Enables:

- QND qubit readout
- Non-local qubit/qubit coupling
- Charge qubit to photon conversion
- Potentially spin qubit to photon conversion
- Essential for quantum information processing with semiconductors
Stockklauser, Scarlino *et al.*, PRX 7, 011030 (2017)
 Mi *et al.*, Science 355, 156 (2017)



Makes many/all features of circuit QED accessible to research and development on semiconductor nano-structures

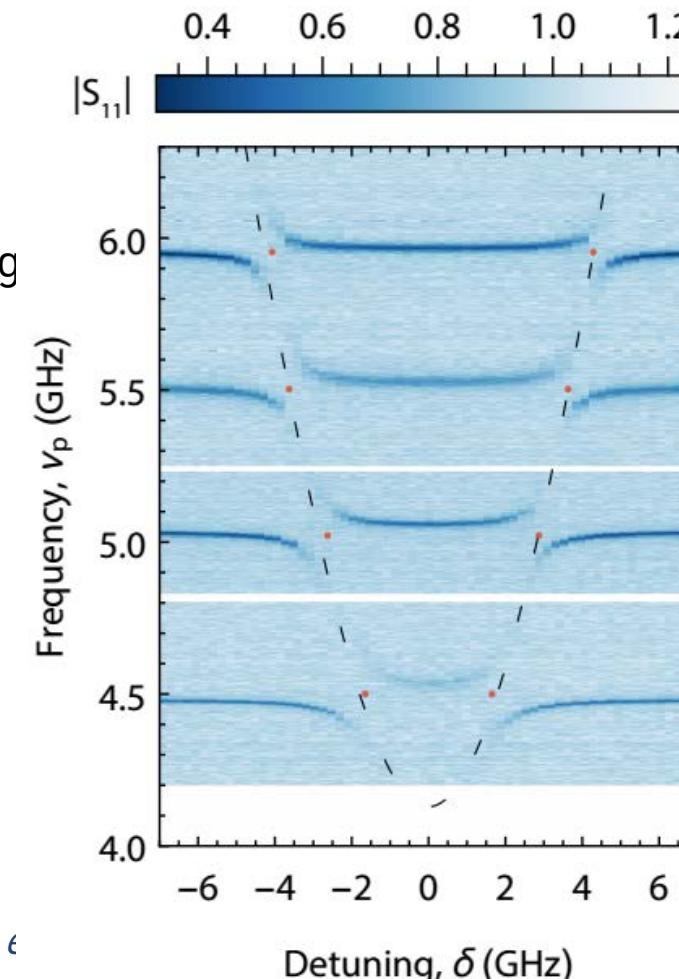
Two Approaches to Qubit Spectroscopy

Tunable resonator spectroscopy

Fixed tunnel coupling
 $2t = 4.13 \text{ GHz}$

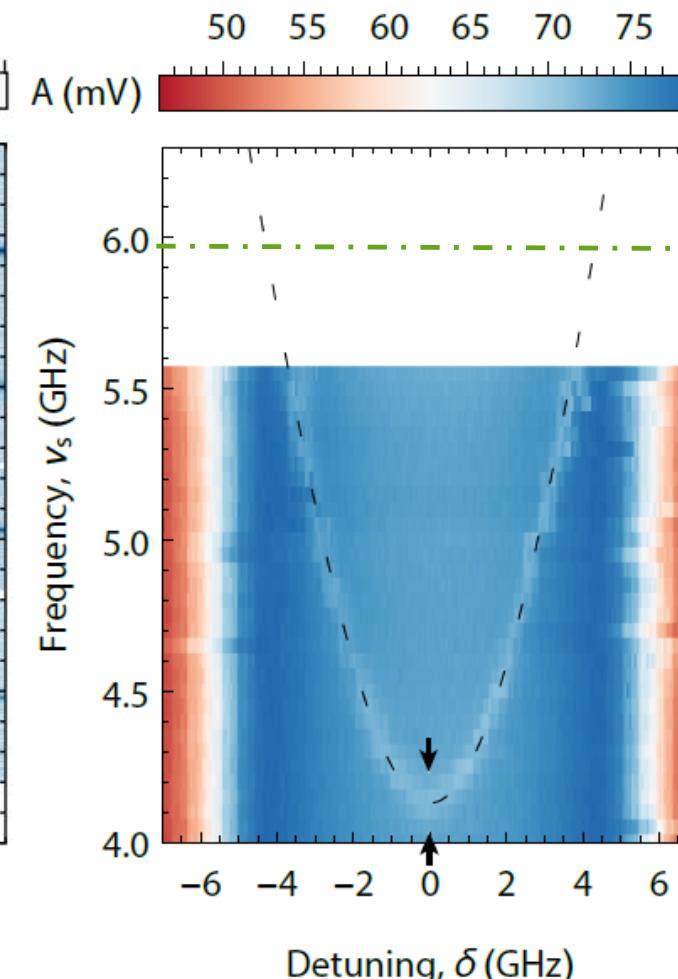
$$\nu_r(\Phi_m) = \nu_q \quad (\bullet)$$

$$\nu_q(\delta) = \sqrt{4t^2 + \delta^2} \quad (-)$$



Stockklauser, Scarlino et al.

Inspired by: Schuster et al. PRL 94, 123602 (2005).



Two-tone spectroscopy

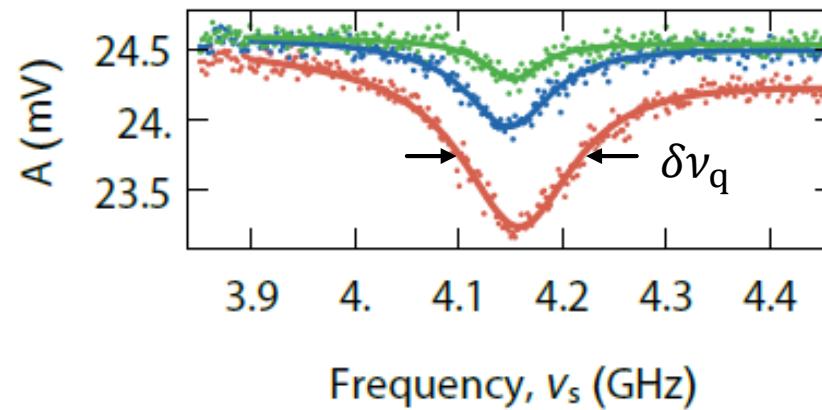
Fixed probe frequency
 $\nu_p = \nu_r = 5.947 \text{ GHz}$

Spectroscopy frequency
 ν_s

$$\nu_q(\delta) = \sqrt{4t^2 + \delta^2}$$

Drive Strength Dependence of Qubit Line-Shape

Two-tone spectroscopy measurement

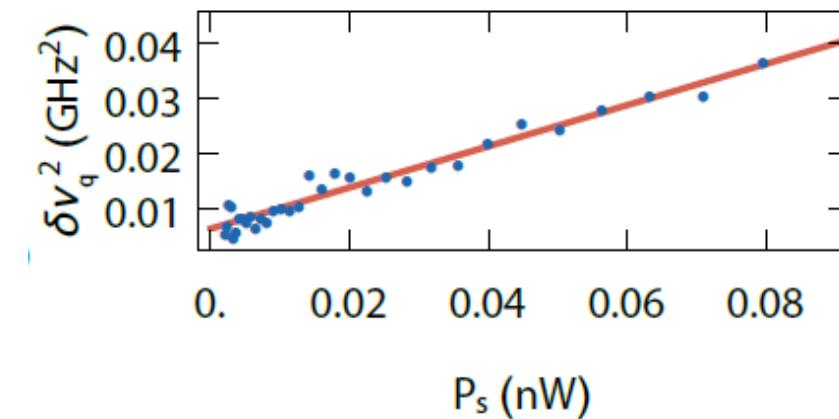


- Power broadening and saturation with spectroscopy drive strength P_s
- Low power limit reveals coherence

Stockklauser, Scarlino *et al.*, PRX7, 011030 (2017).

Inspired by: Schuster *et al.* PRL 94, 123602 (2005).

Qubit line width $\delta\nu_q^2$ vs. drive strength P_s



- For $P_s \rightarrow 0$

$$\frac{1}{T_2} = \pi \delta\nu_q$$

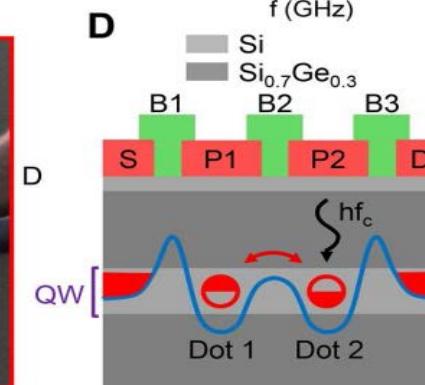
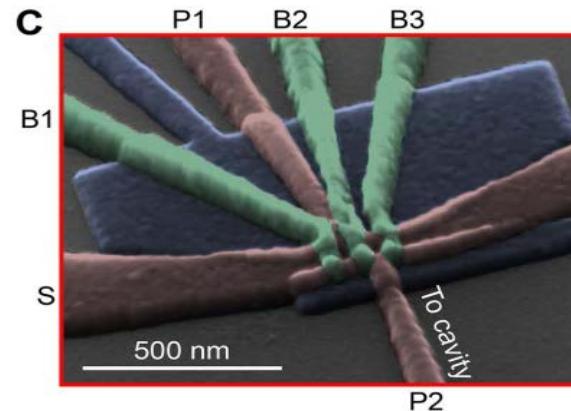
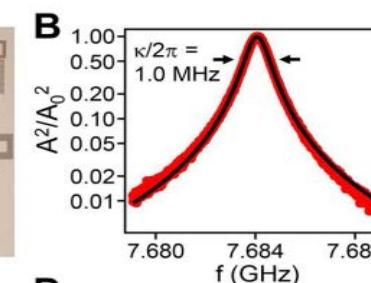
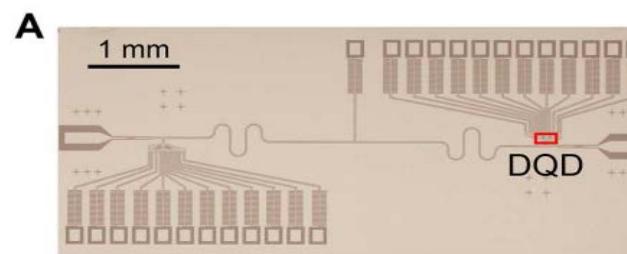
$$\gamma_2/2\pi = 40 \text{ MHz}$$

- Surprisingly small linewidth for charge states in piezoelectric GaAs
- Even better coherence observed in subsequent experiments

Recent Companion Experiments on Strong Coupling

Si\SiGe DQD (dipolar coupling)

X. Mi et al., Science 355, 156-158 (2017)

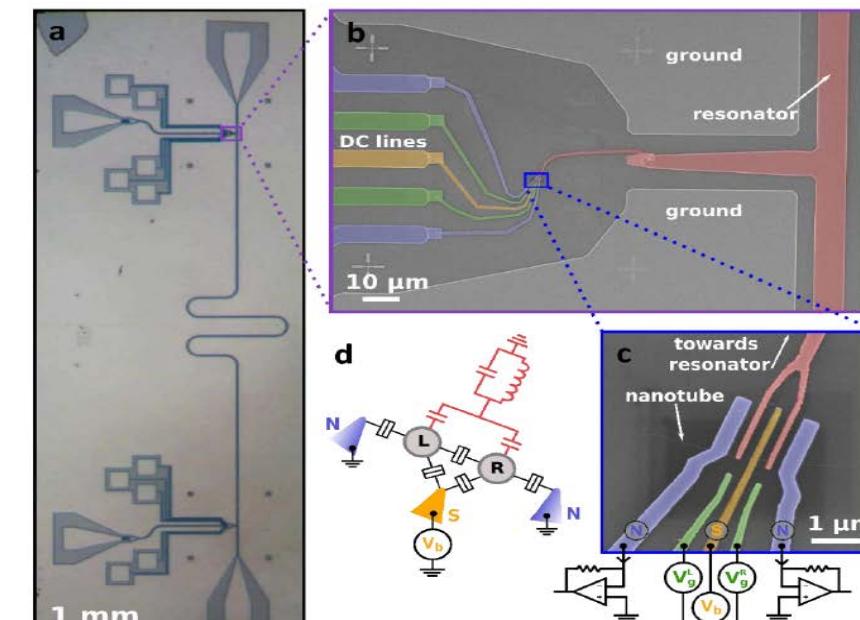


- $Z_0 = 50 \Omega$
- $g/2\pi \approx 6.7 \text{ MHz}$
- $(\kappa, \gamma)/2\pi \approx (1, 2.6) \text{ MHz}$

strong coupling regime
($g > \kappa, \gamma$)

Carbon Nanotube DQD with superconducting leads

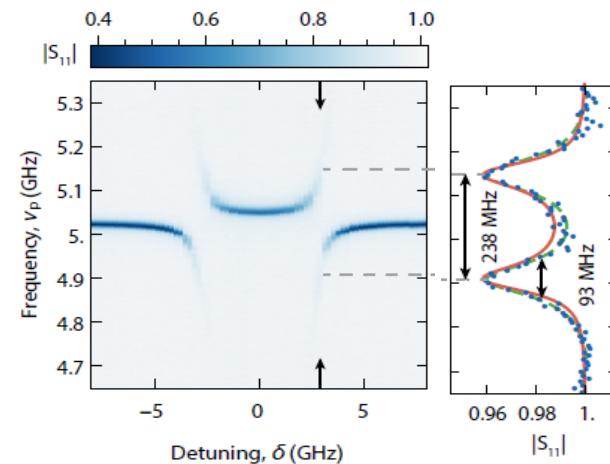
L. E. Bruhat et al., arXiv:1612.05214



- $Z_0 = 50 \Omega$
- $g/2\pi \approx 10 \text{ MHz}$
- $(\kappa, \gamma)/2\pi \approx (1, 4) \text{ MHz}$

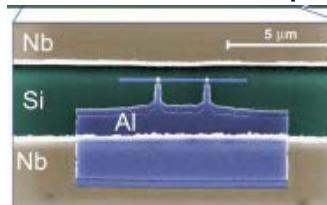
Conclusion and Perspectives

Strong coupling in semiconductor QDs



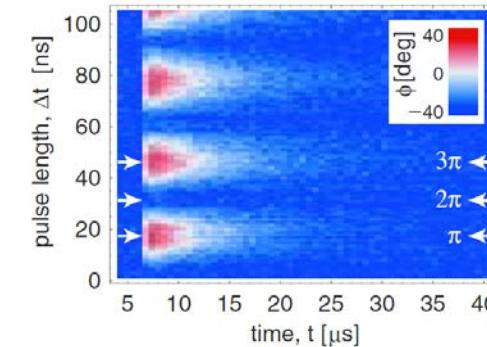
Stockklauser, Scarlino *et al.*, *PRX*7, 011030 (2017).
Mi *et al.*, *Science* 355, 156 (2017)

- coherent coupling to other types of qubits



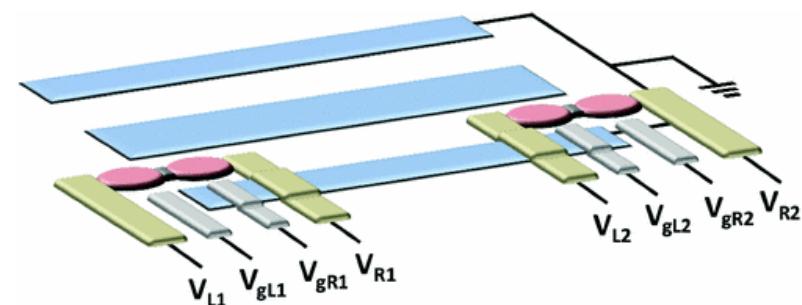
Nature 431, 162 (2004)

- Time-resolved measurements with dispersive readout



PRL 95, 060501 (2005)

- Non-local coherent coupling of multiple DQDs



Bergenfeldt *et al.*, *PRB* 87, 195427 (2013)
Delbecq *et al.*, *Nat. Comm.* 4, 1400 (2013)